

# Scaled Superconducting Nanowire Detectors in Photonic Circuits

**Hong Tang**

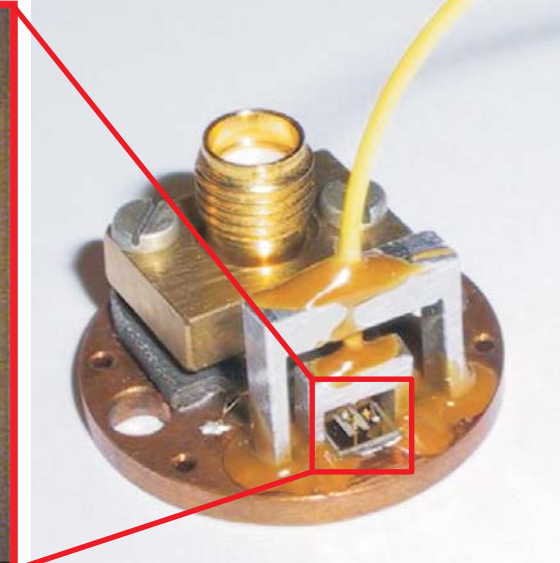
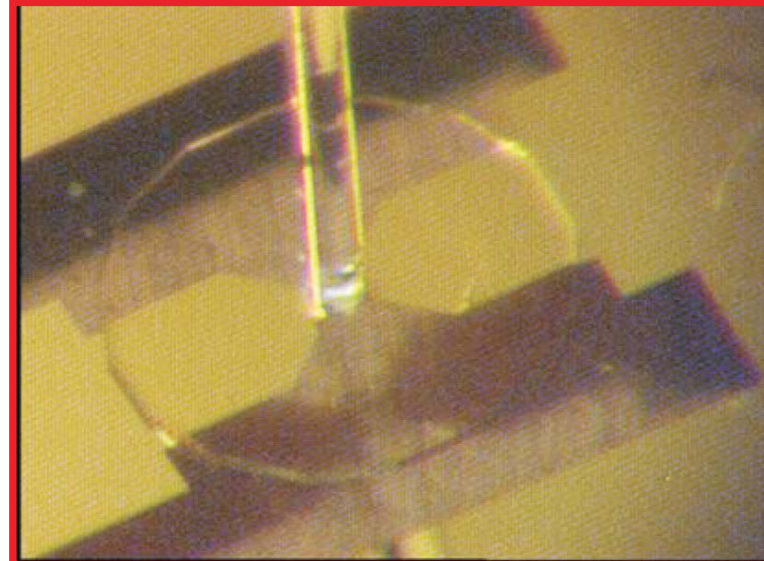
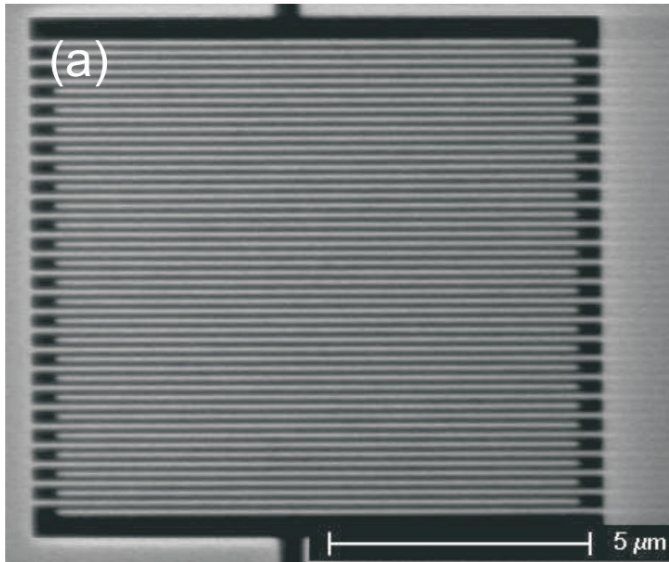
Yale University, Dept. of Electrical Engineering, New Haven, CT, USA



## Desired features of single-photon detectors:

- high detection efficiency
- low dark count rate
- high speed
- high timing accuracy
- sensitivity from VIS-MIR
- many of them!

# Superconducting single-photon detectors

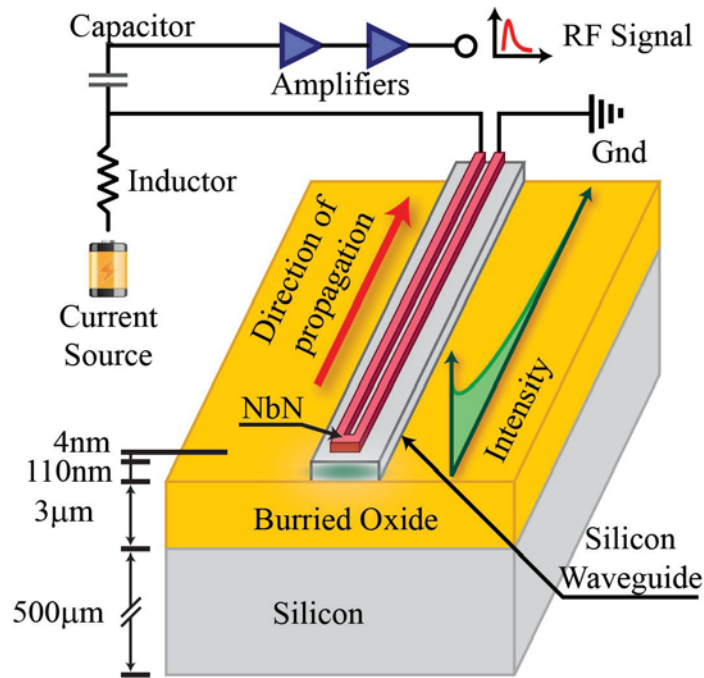


Dorenbos, TU-Delft (2011)

- meander of nanowires fabricated from 4nm NbN thin-film
- active area  $\sim 10 \times 10 \mu\text{m}$ , nanowire widths  $\sim 100\text{nm}$
- absorb photons under normal incidence from optical fiber
- cool below critical temperature ( $T_c = 11\text{K}$ )
- dc-bias close to critical current ( $I_c = 10\text{-}30\mu\text{A}$ )
- $\sim 20\%$  single pass absorption efficiency



## SSPD fully integrated with nanophotonic circuitry



### NbN on Si:

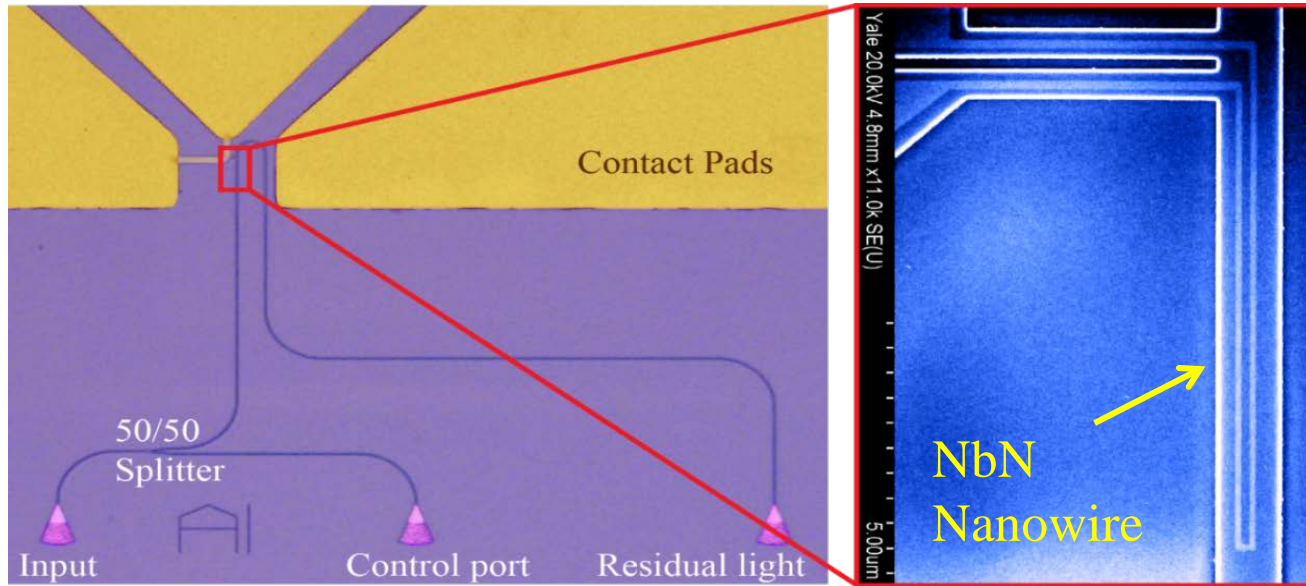
*W.H.P. Pernice et al.,*  
Nat. Comm. 3, 1325 (2012)

*Schuck et al.,*  
IEEE Trans. ASC 23, 2201007 (2013)

### NbTiN on SiN:

*Schuck et al.,*  
APL 102, 051101 (2013)

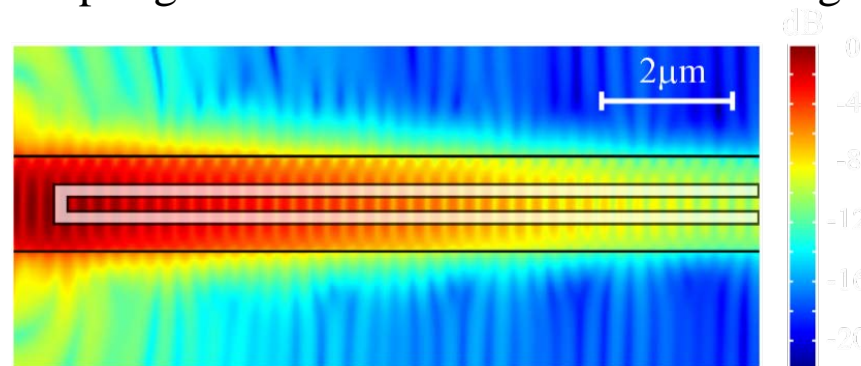
*Schuck et al.,*  
Sci. Rep. 3, 1893 (2013)  
*Schuck et al.,*  
APL 102, 191104 (2013)



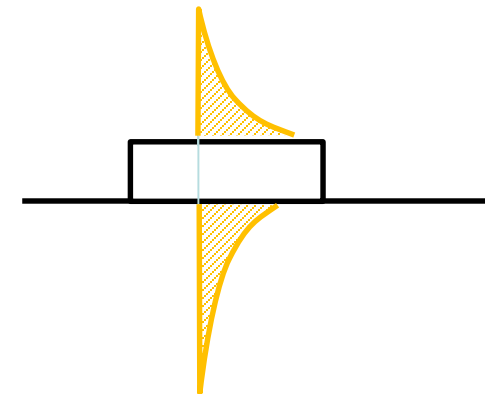
W. Pernice, C. Schuck, O. Minaeva, M. Li, G. N. Goltsman, A. V. Sergienko, H. X. Tang, Nature Communications, 2012

## Travelling wave design

- Waveguide coupling allows for absorption engineering
- Plasmonic coupling of NbN wire to evanescent waveguide mode

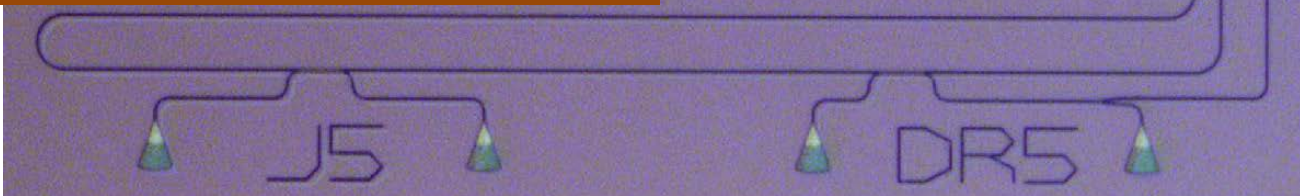
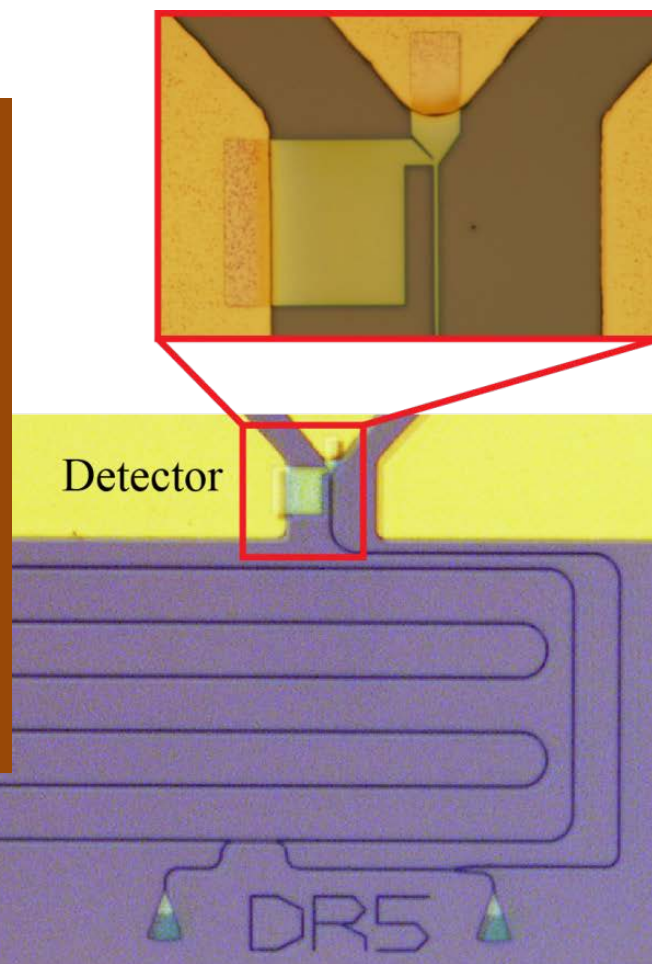
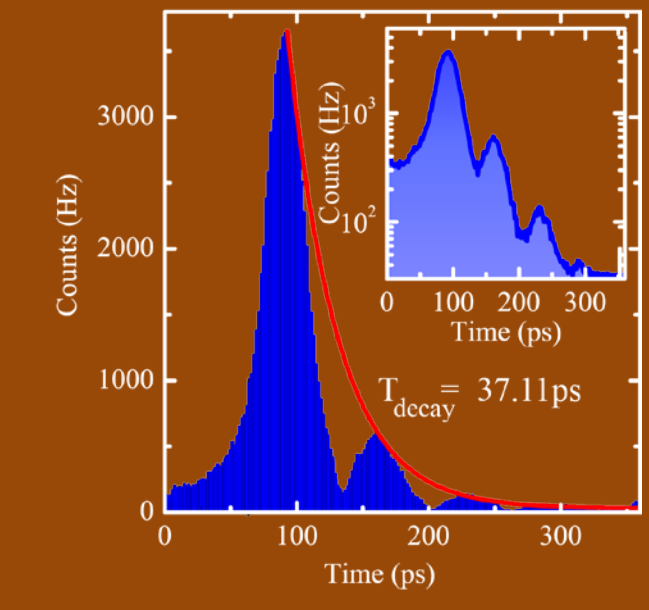
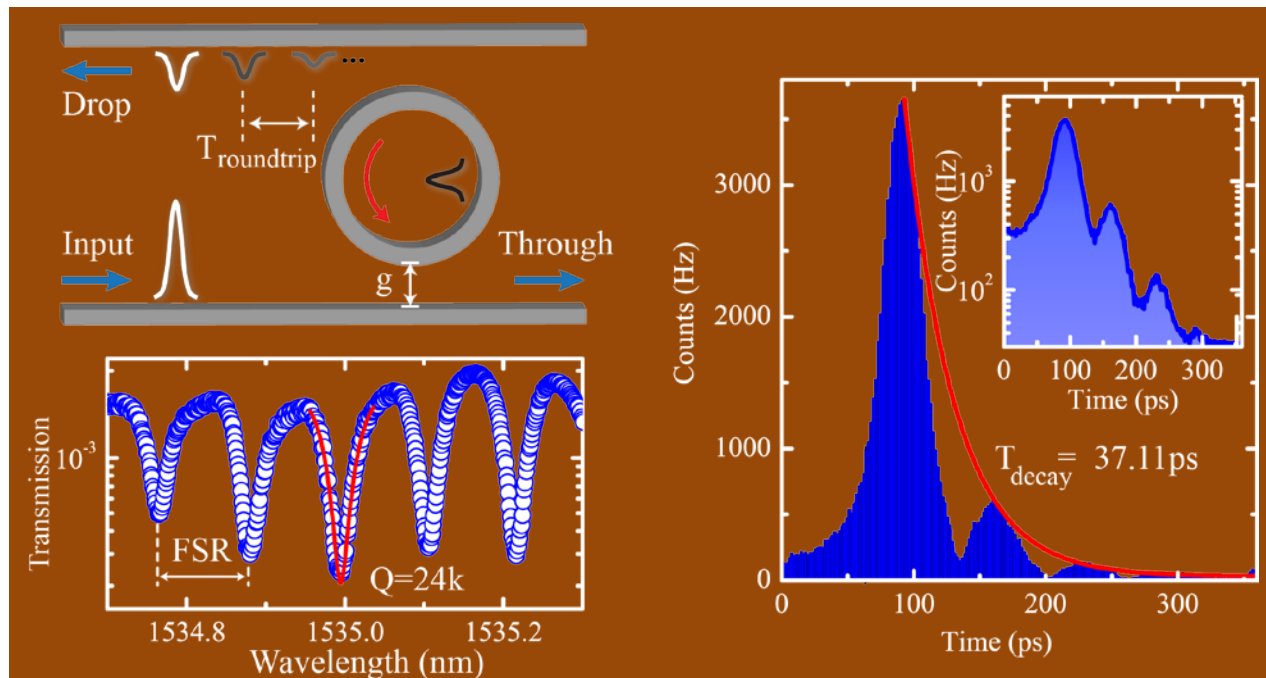
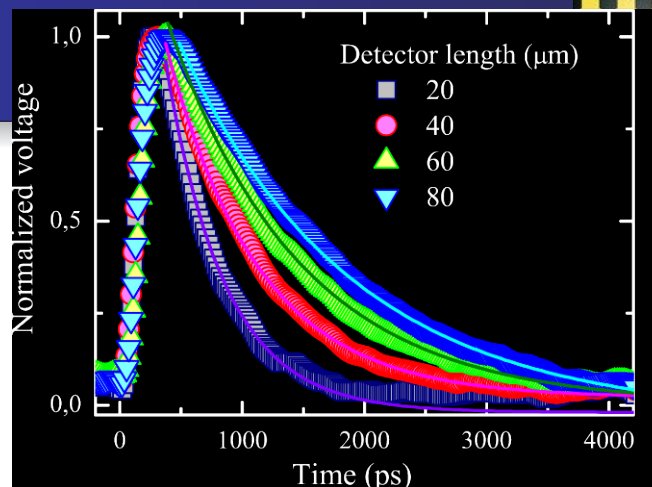


Absorption rate: 1dB/ $\mu$ m

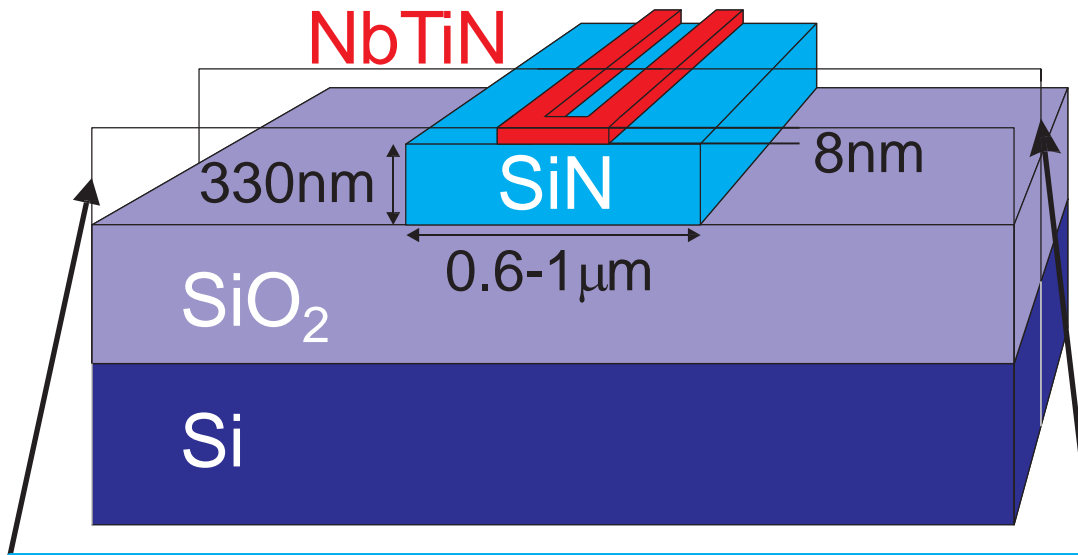


# Jitter

- Jitter = 18.4ps
- 5.8mm Ring, Propagation loss of 4dB/cm
- Decay 37ps => round trips are observed



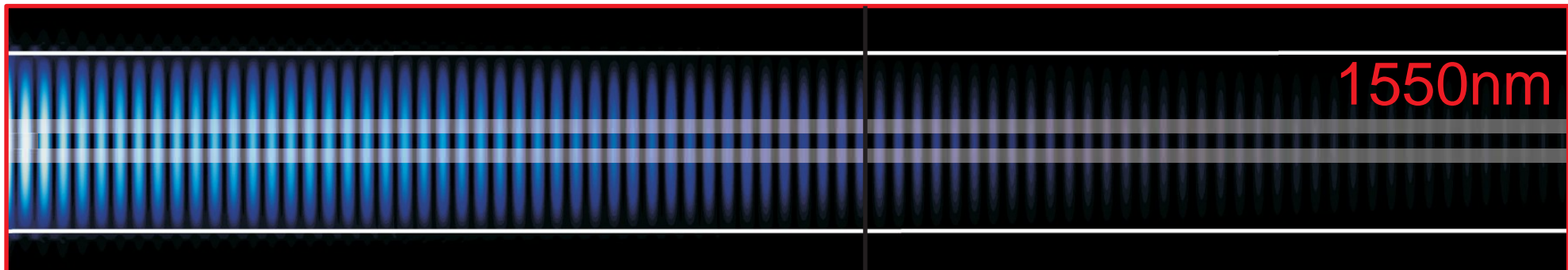
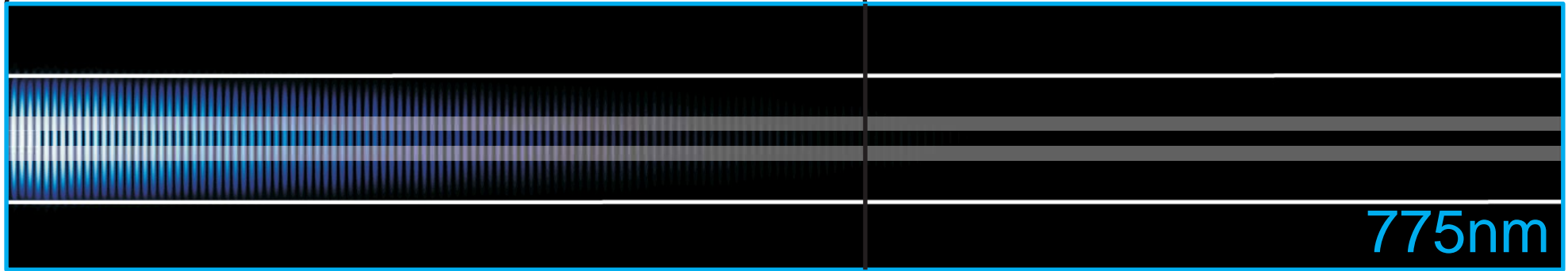
# Efficient photon absorption on-chip



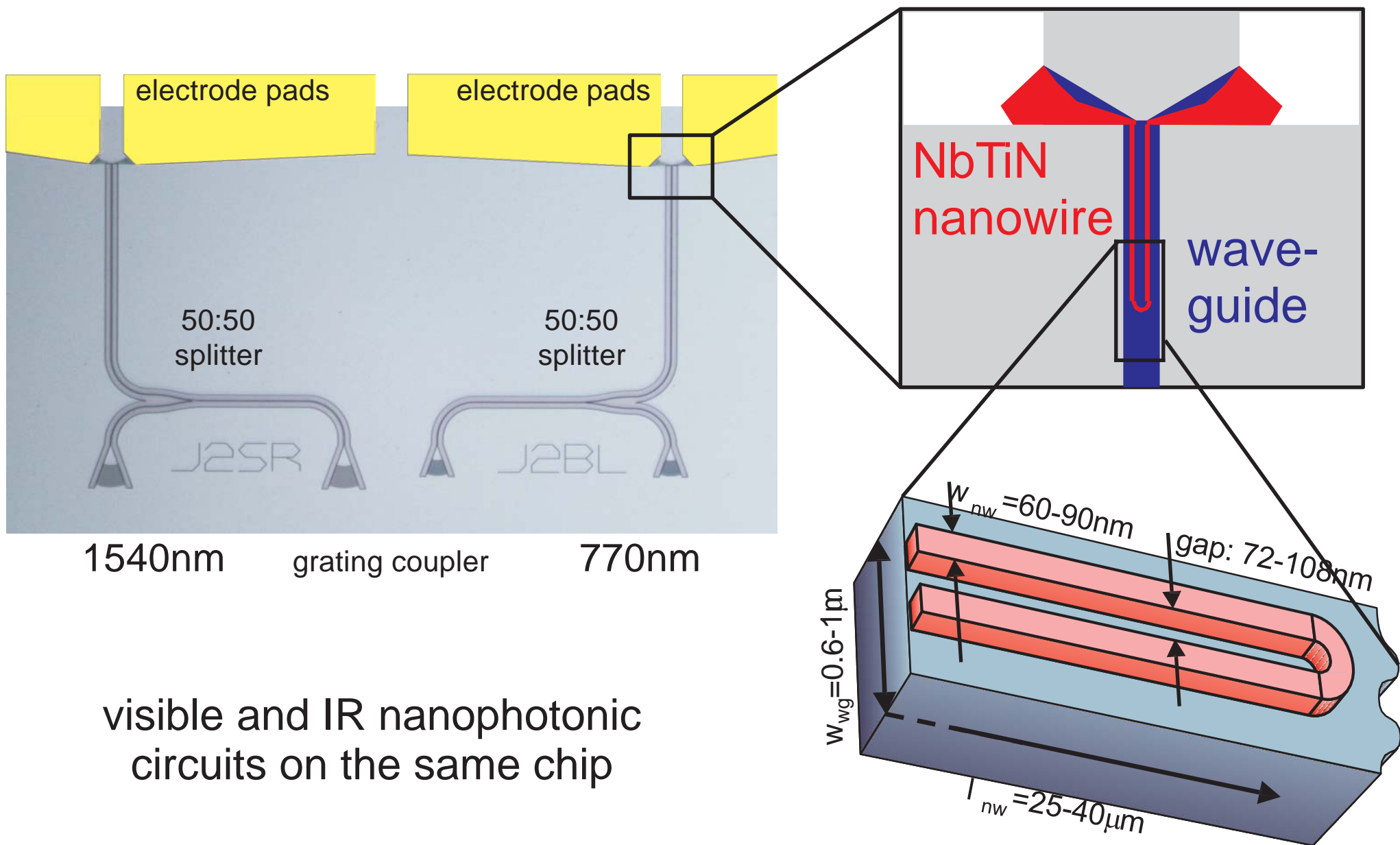
## FDTD-simulations

775nm light: 0.71 dB/μm  
→ 99.9% absorption for 40μm

1550nm light: 0.33 dB/μm  
→ 95.2% absorption for 40μm



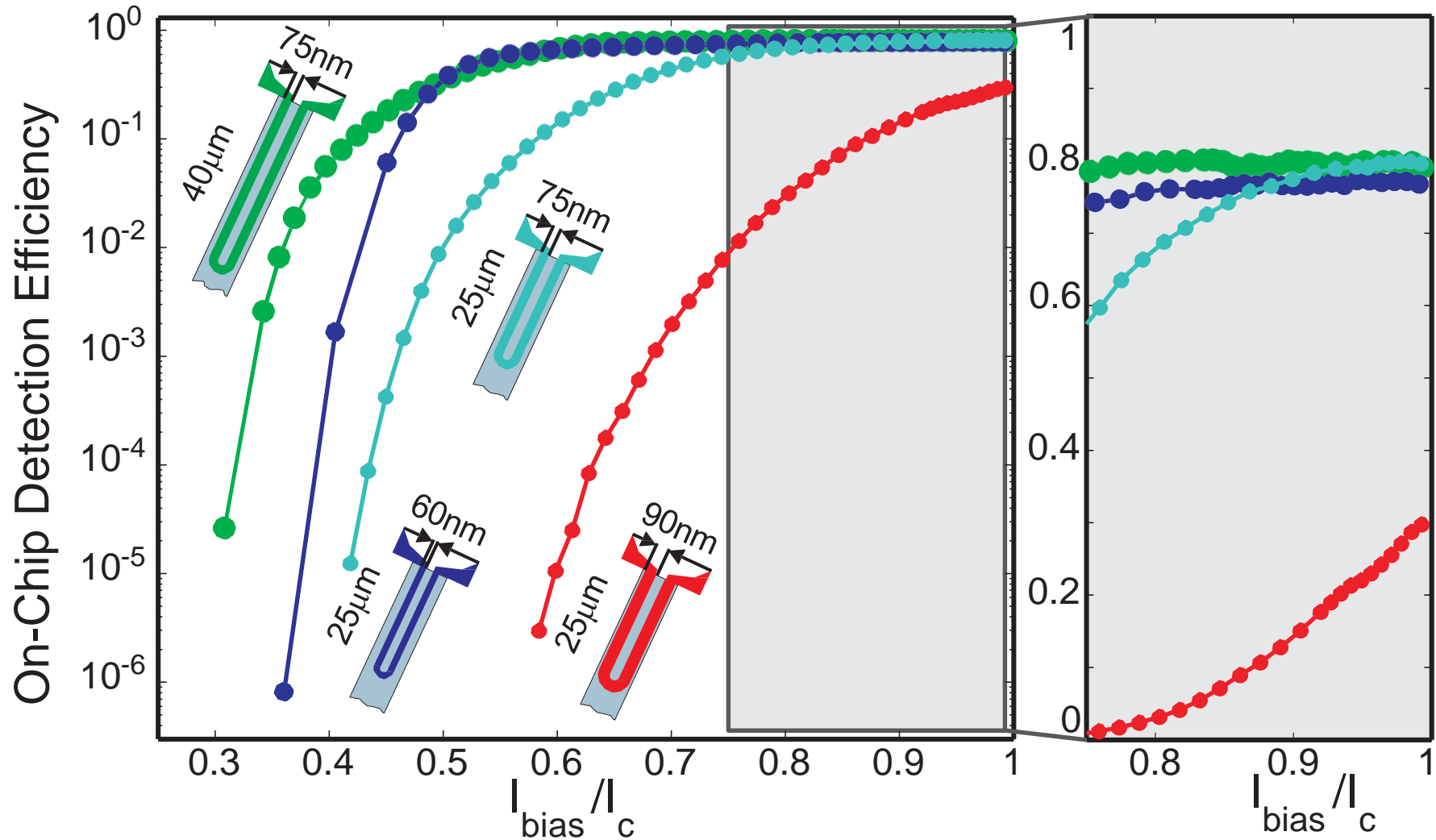
# NbTiN-SSPDs on SiN waveguides



visible and IR nanophotonic circuits on the same chip



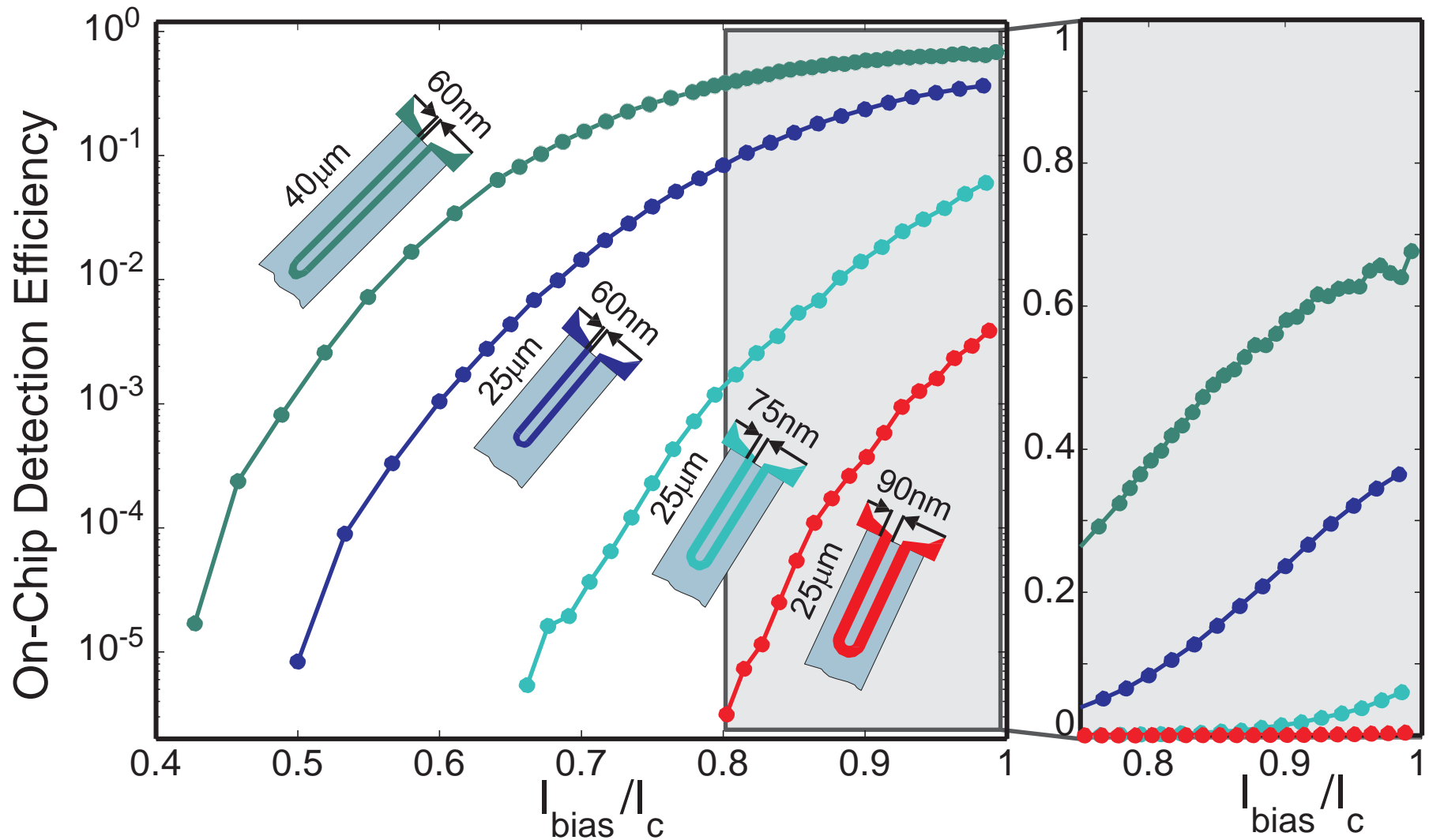
# Detection efficiency: 768nm



Detection efficiency  $\propto$  hotspot size ( $\propto$  photon energy):

saturation @ 80% when hotspot diameter  $\sim$  nanowire width

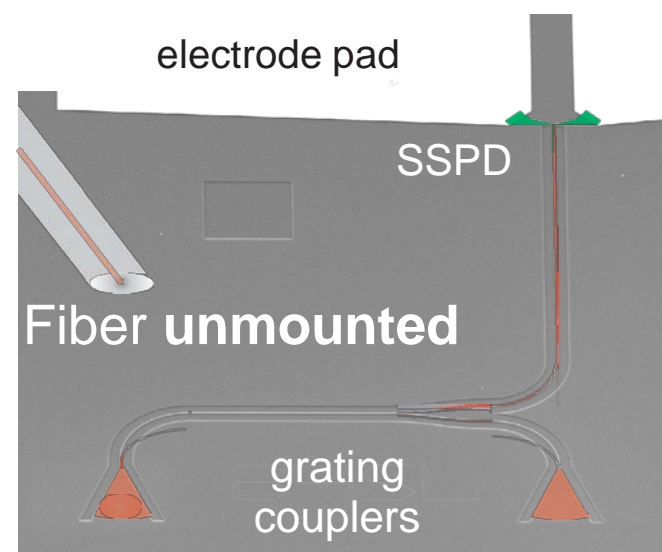
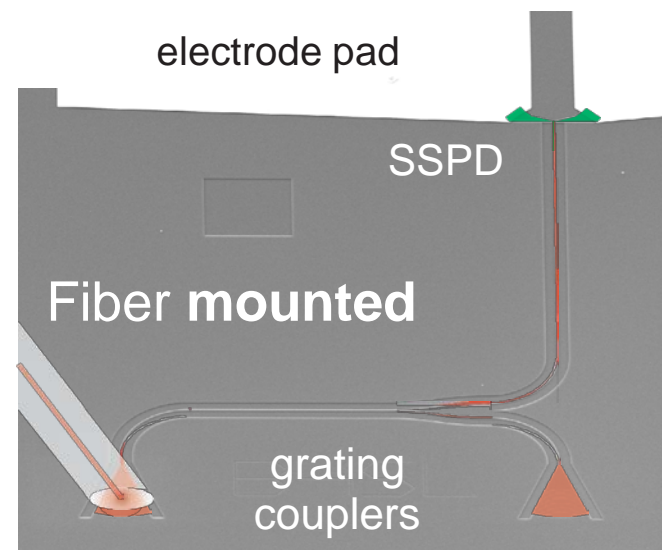
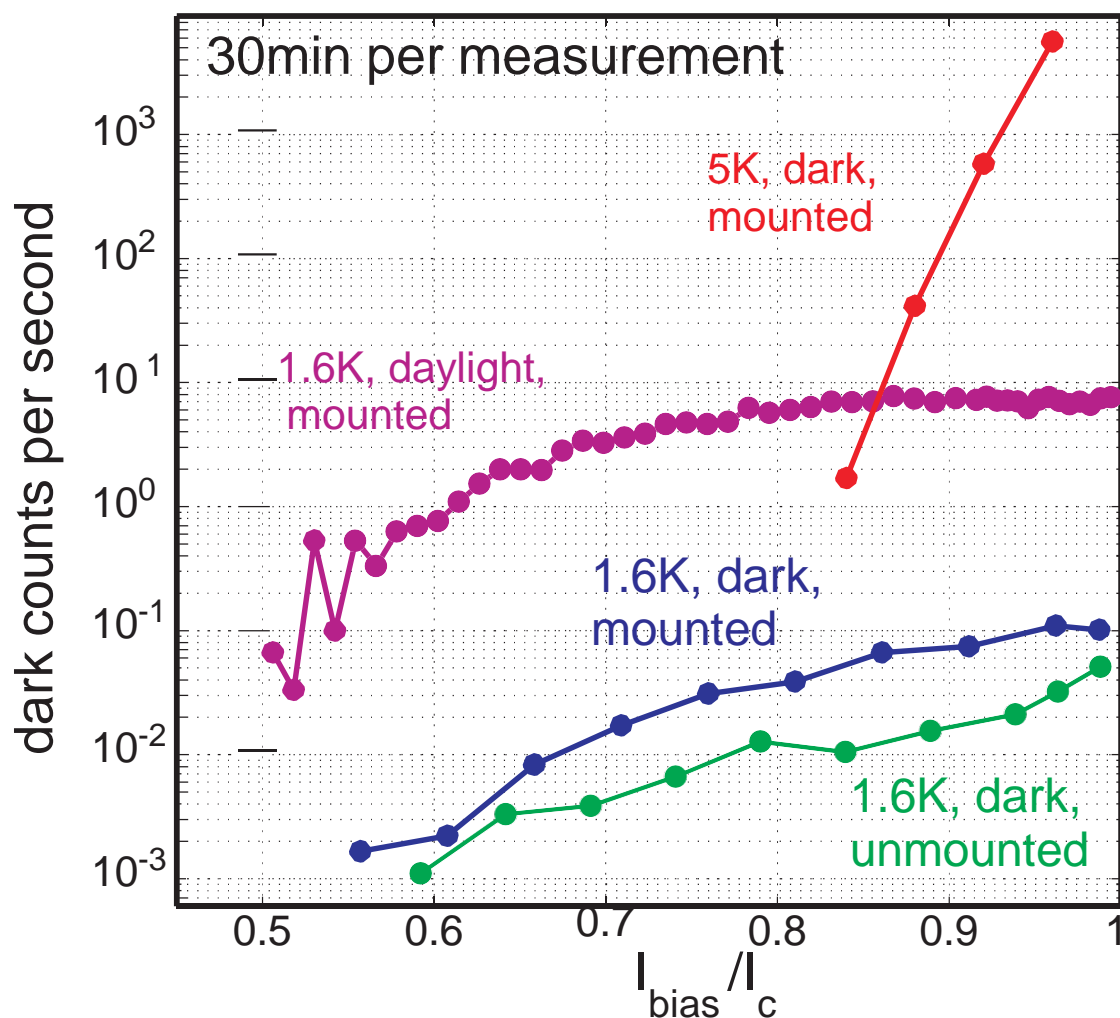
# Detection efficiency: 1542nm



Optimize nanowire geometry for optimal performance:

decrease nanowire width & increase length: 68% OCDE @ 99%  $I_c$

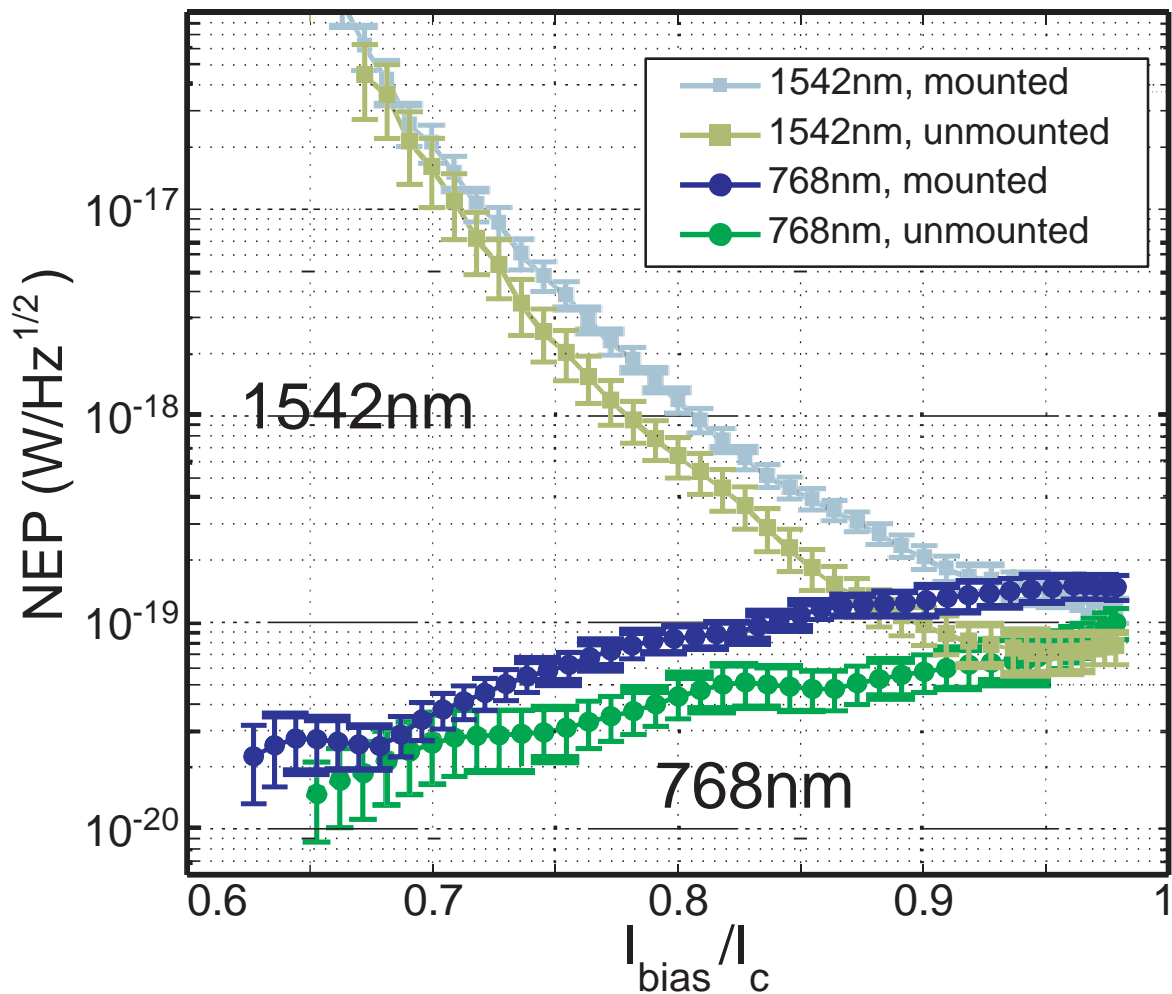
# Low dark count rate



DCR: 1-100mHz (60%-99%  $I_c$ )

1.6K: decoherence mechanisms are suppressed below stray light-level!

# Low noise equivalent power



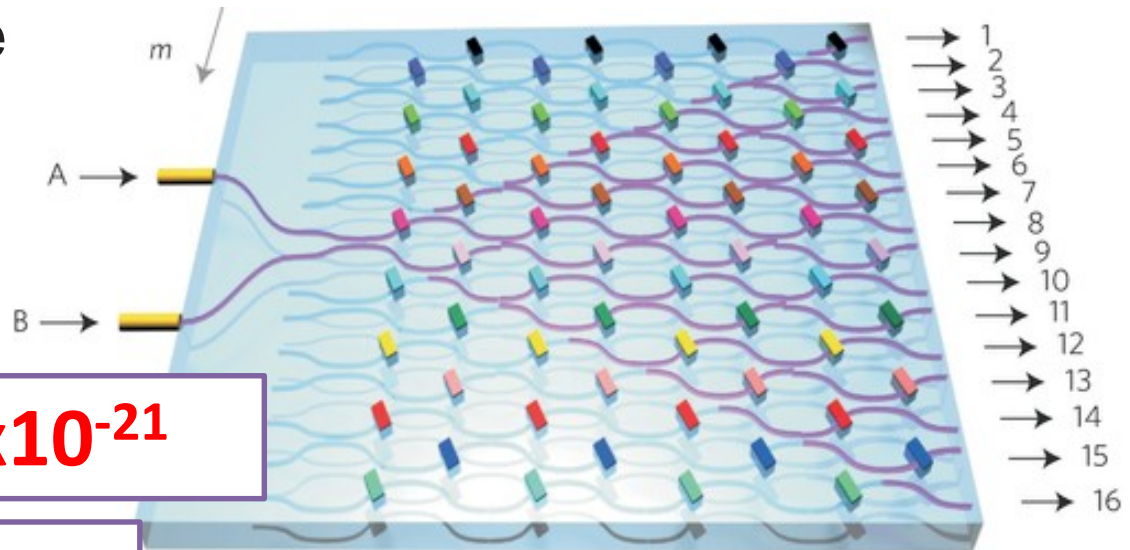
$$\text{NEP} = \frac{h\nu (2 \text{ DCR})^{1/2}}{DE_{\text{on-chip}}}$$

768nm (on-chip) $2 \times 10^{-20}$ @ 65% $I_c$	1542nm (on-chip) $7 \times 10^{-20}$ @ 94% $I_c$	1542nm (system) $8 \times 10^{-18}$ @ 95% $I_c$
----------------------------------------------------	-----------------------------------------------------	----------------------------------------------------



- Applications:
- **integrated quantum optics**
  - quantum cryptography
  - **sensing (optical time domain reflectometry)**
  - spectroscopy & biomedical applications

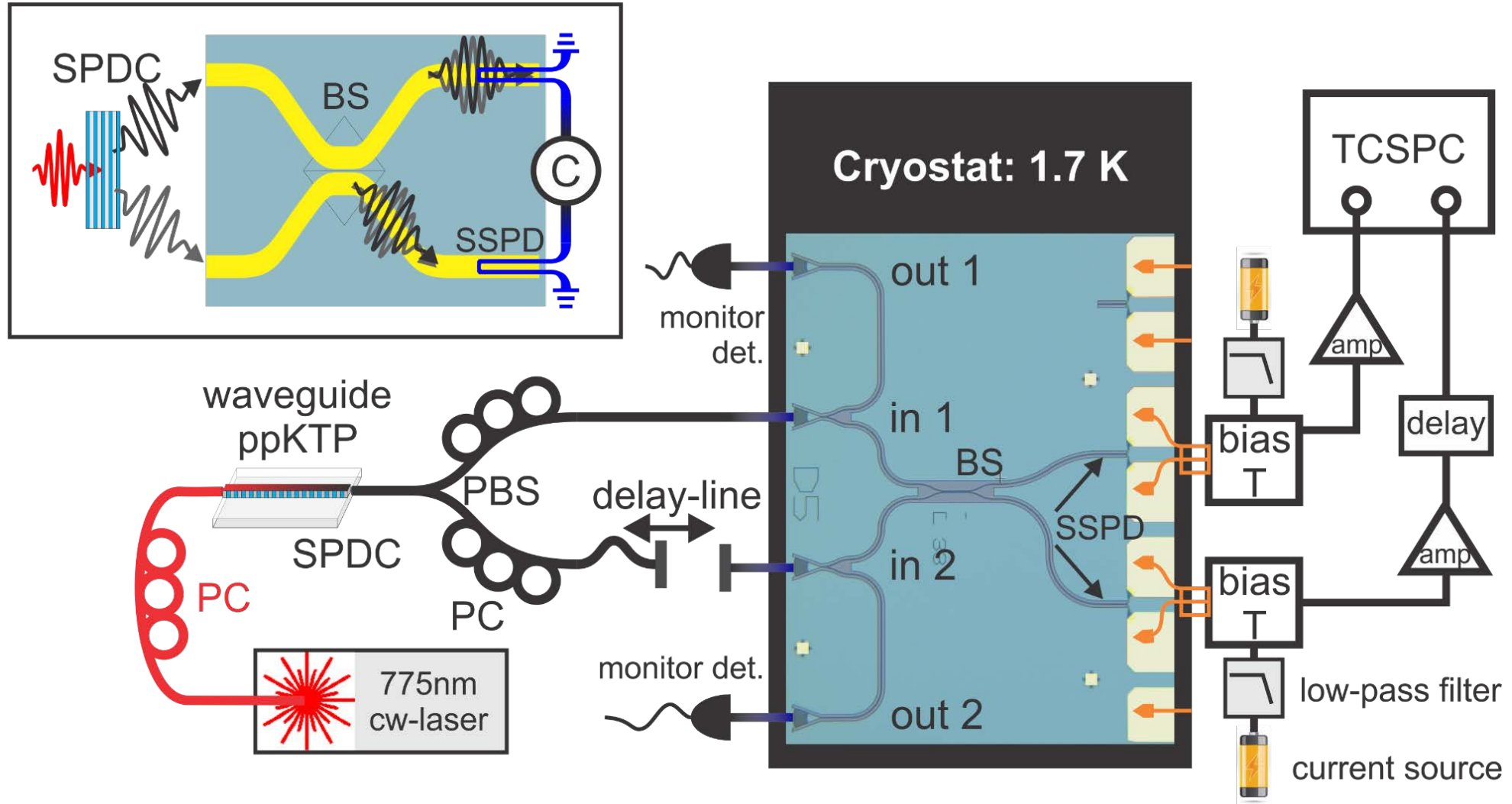
**Scalable** quantum information processing needs efficient interfaces between source circuit & detectors.



$$(5\%)^{16} = 1.5 \times 10^{-21}$$

$$(90\%)^{16} = 0.20$$

# Building a HOM interferometer on a chip

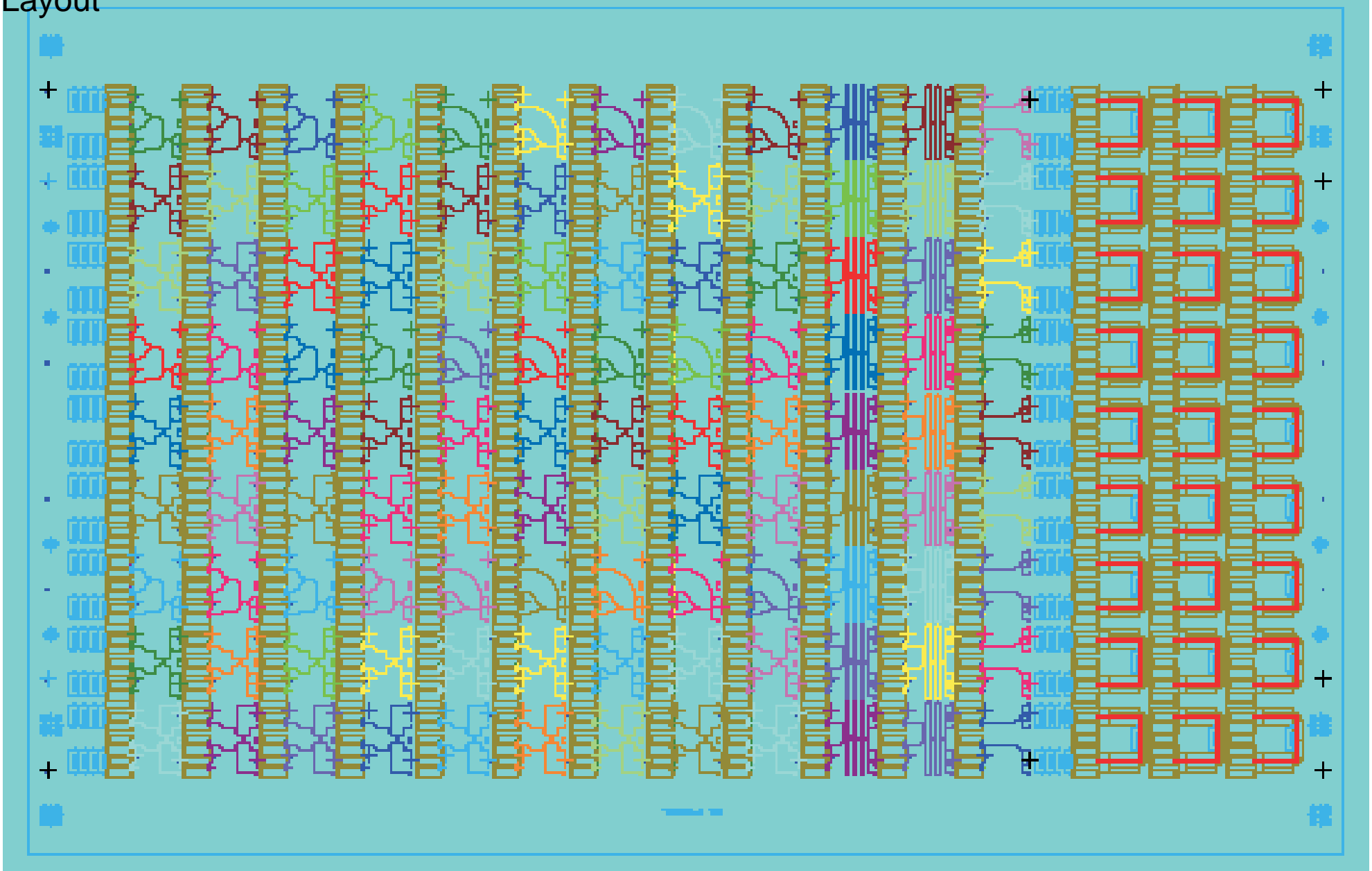


Two detectors + 1 Beam Splitter

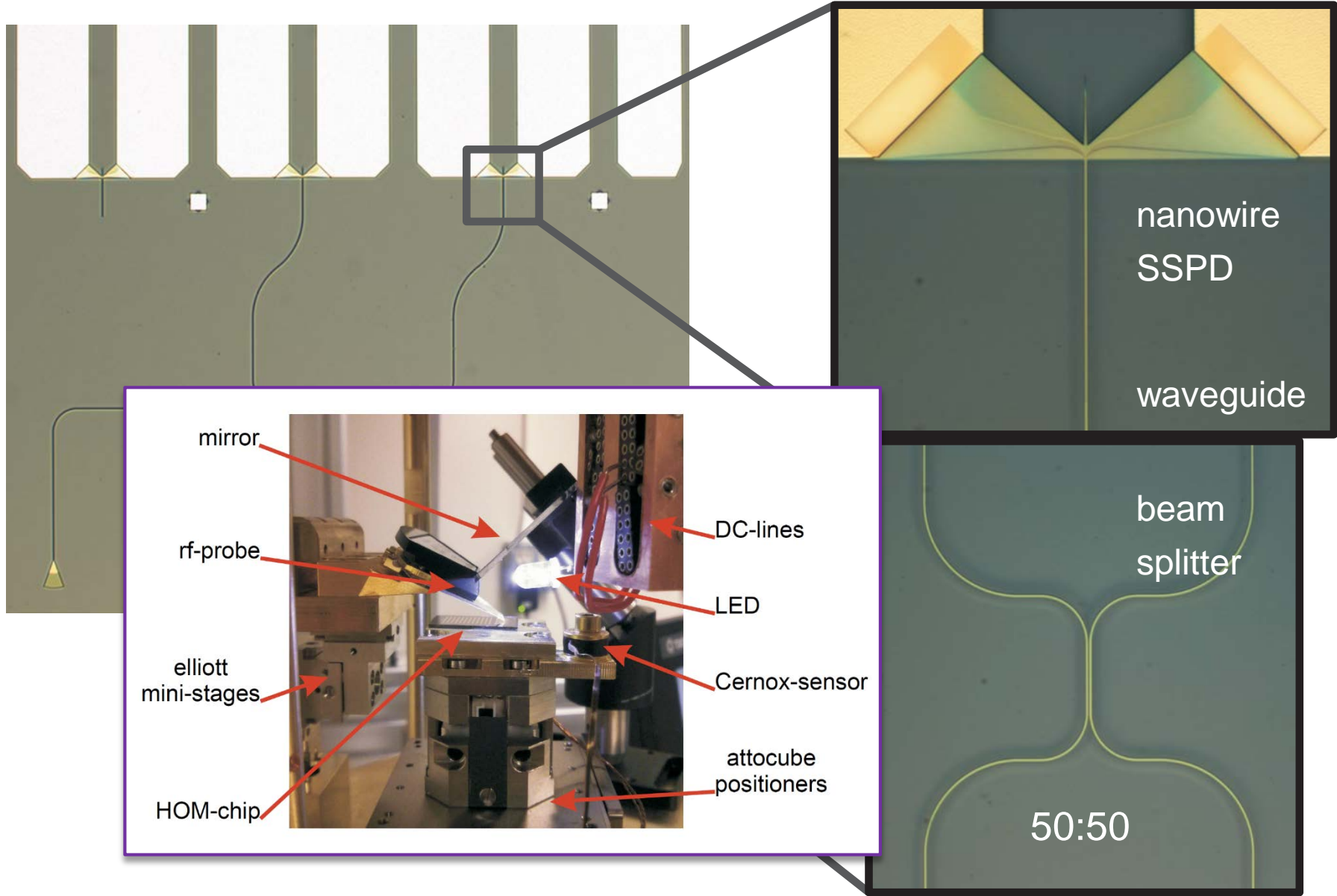
# On-chip HOM with integrated detector



Layout

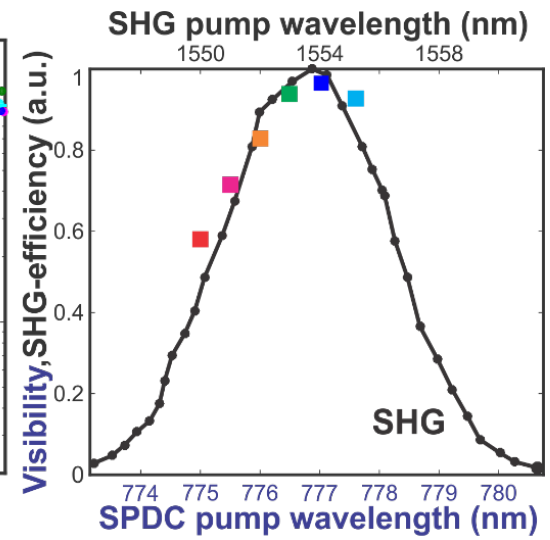
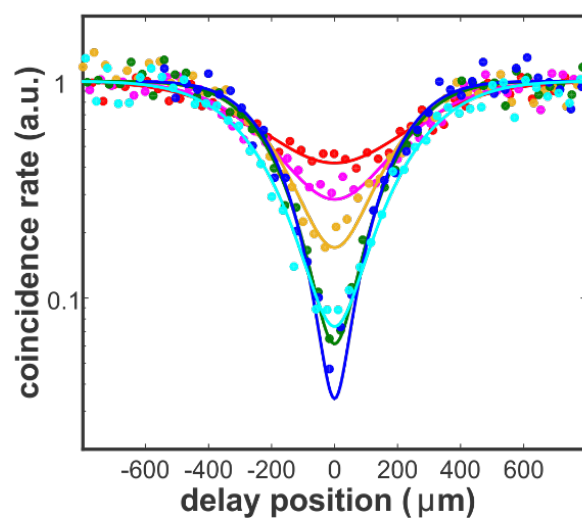
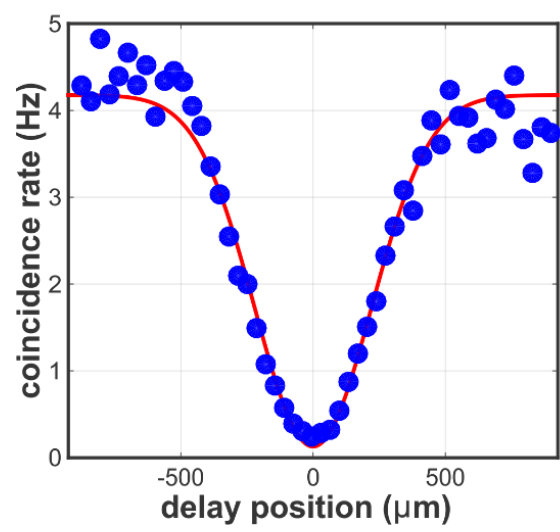
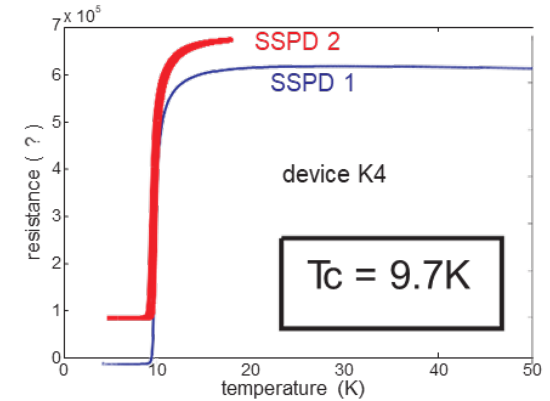
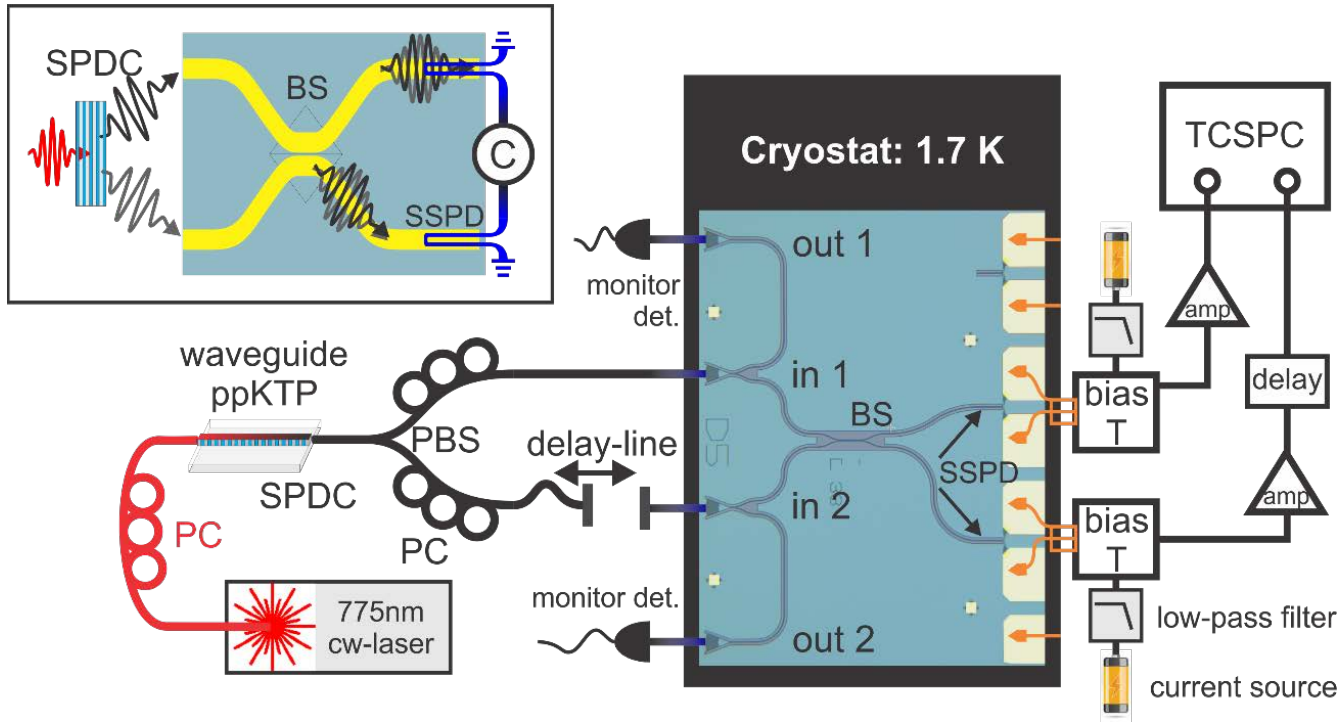


# HOM + 2 SSPD device

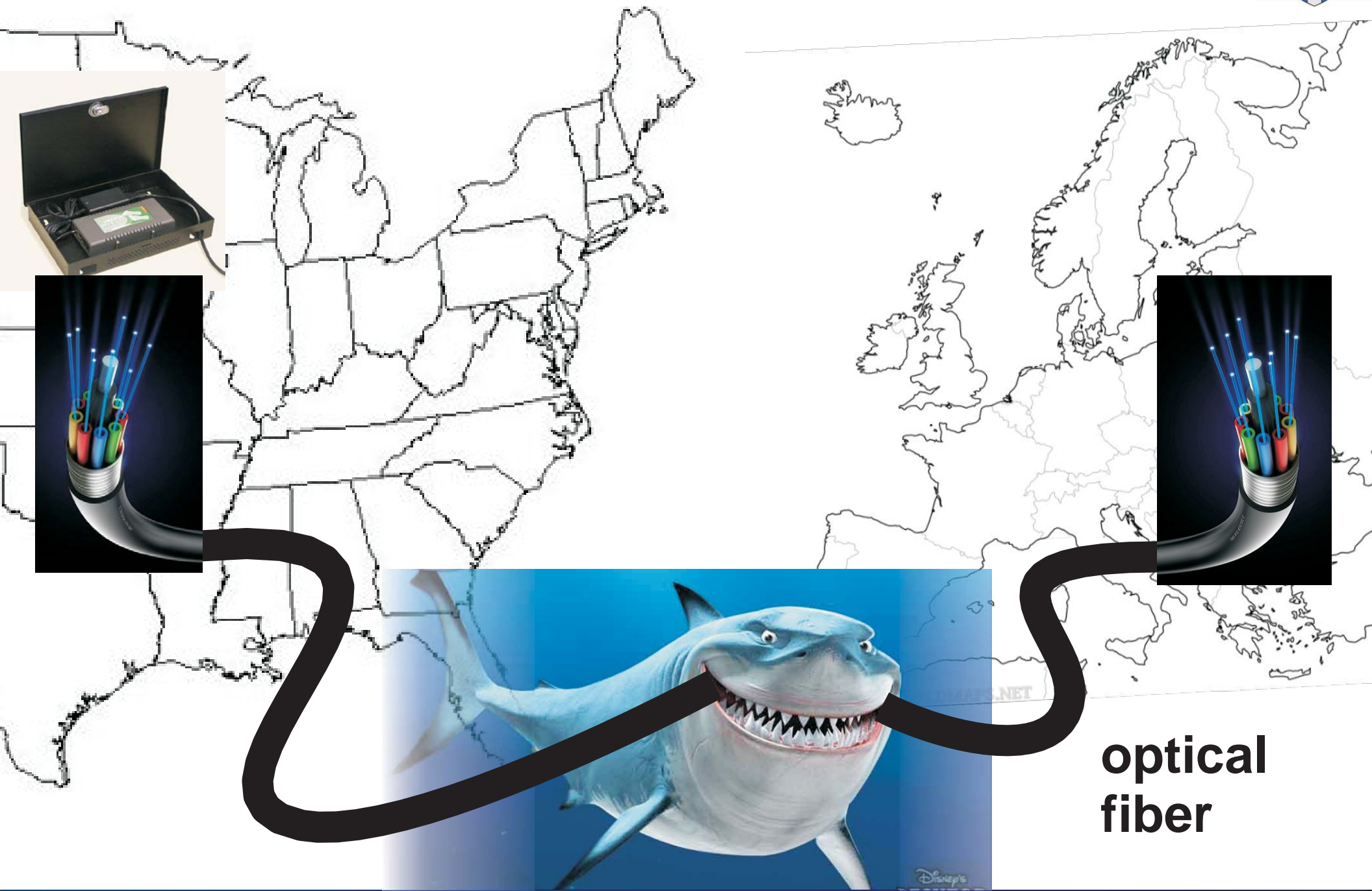




# HOM + 2 SSPD device

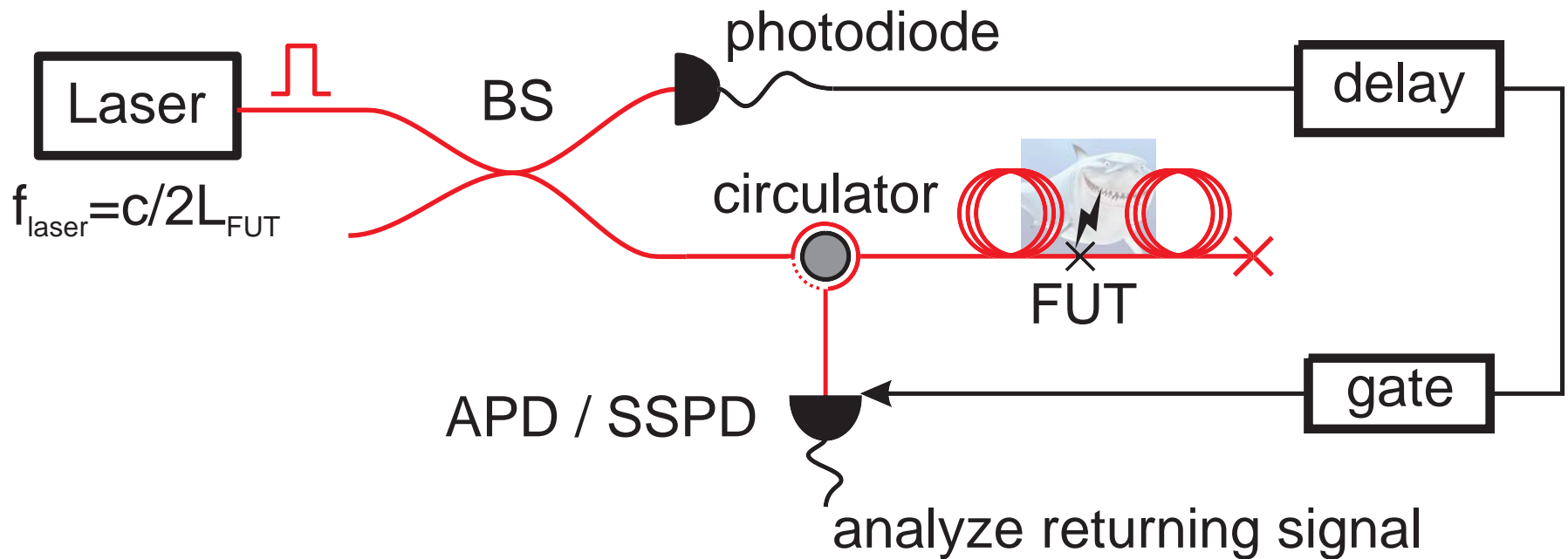


# Optical Time Domain Reflectometry



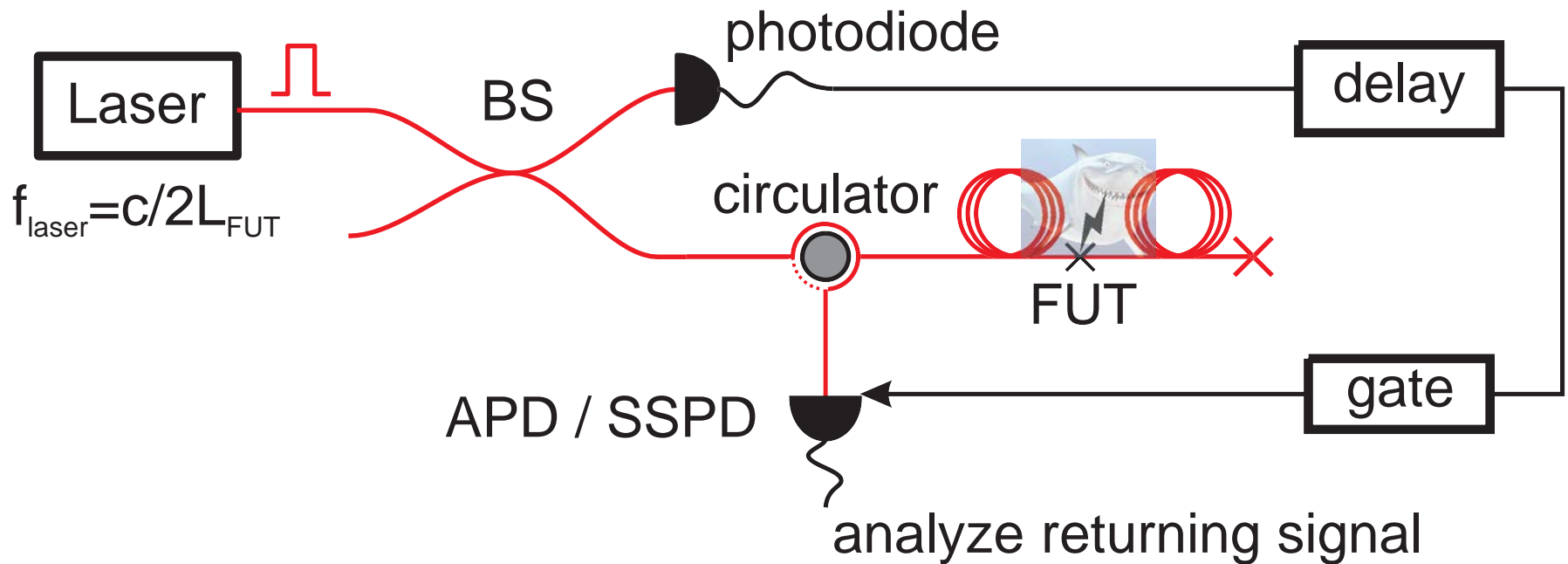
**optical  
fiber**

# Optical Time Domain Reflectometry



OTDR: Diagnose physical condition of a (long) optical fiber *in situ*.

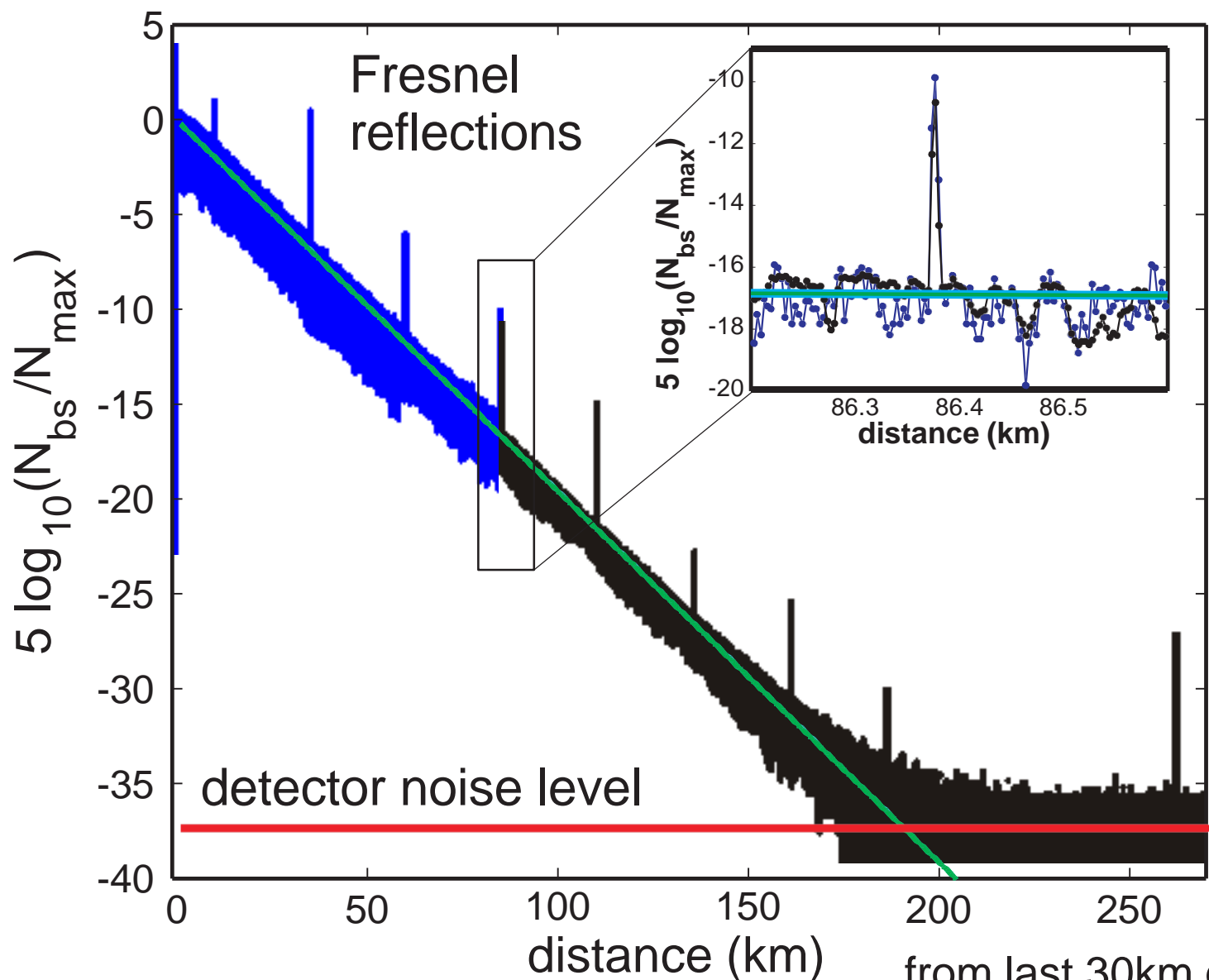
- localization of defects
- fiber loss & attenuation properties
- refractive index changes



## Advantages SSPD vs. APD:

- lower detector noise (NEP)
- free-running (no gating)
- larger dynamic range
- no afterpulsing, charge persistence effects, deadzones

# OTDR: dynamic range



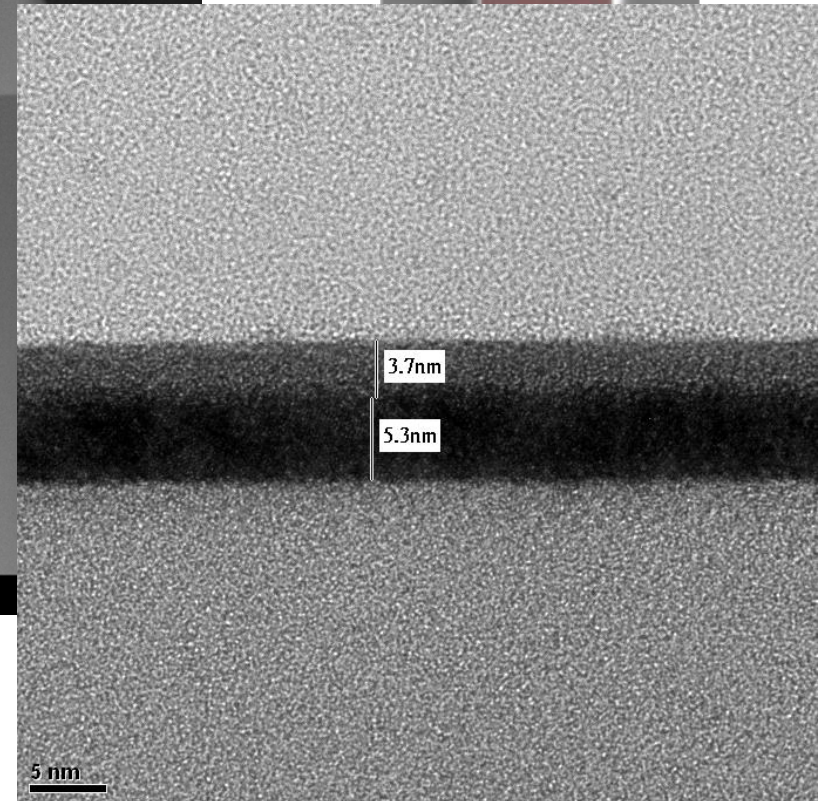
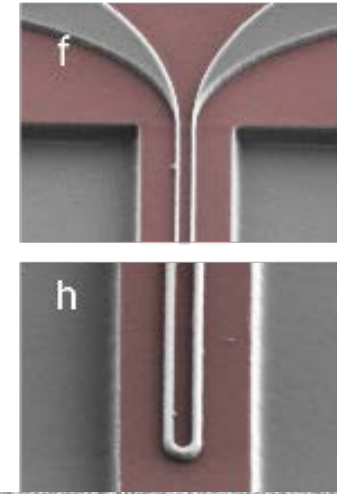
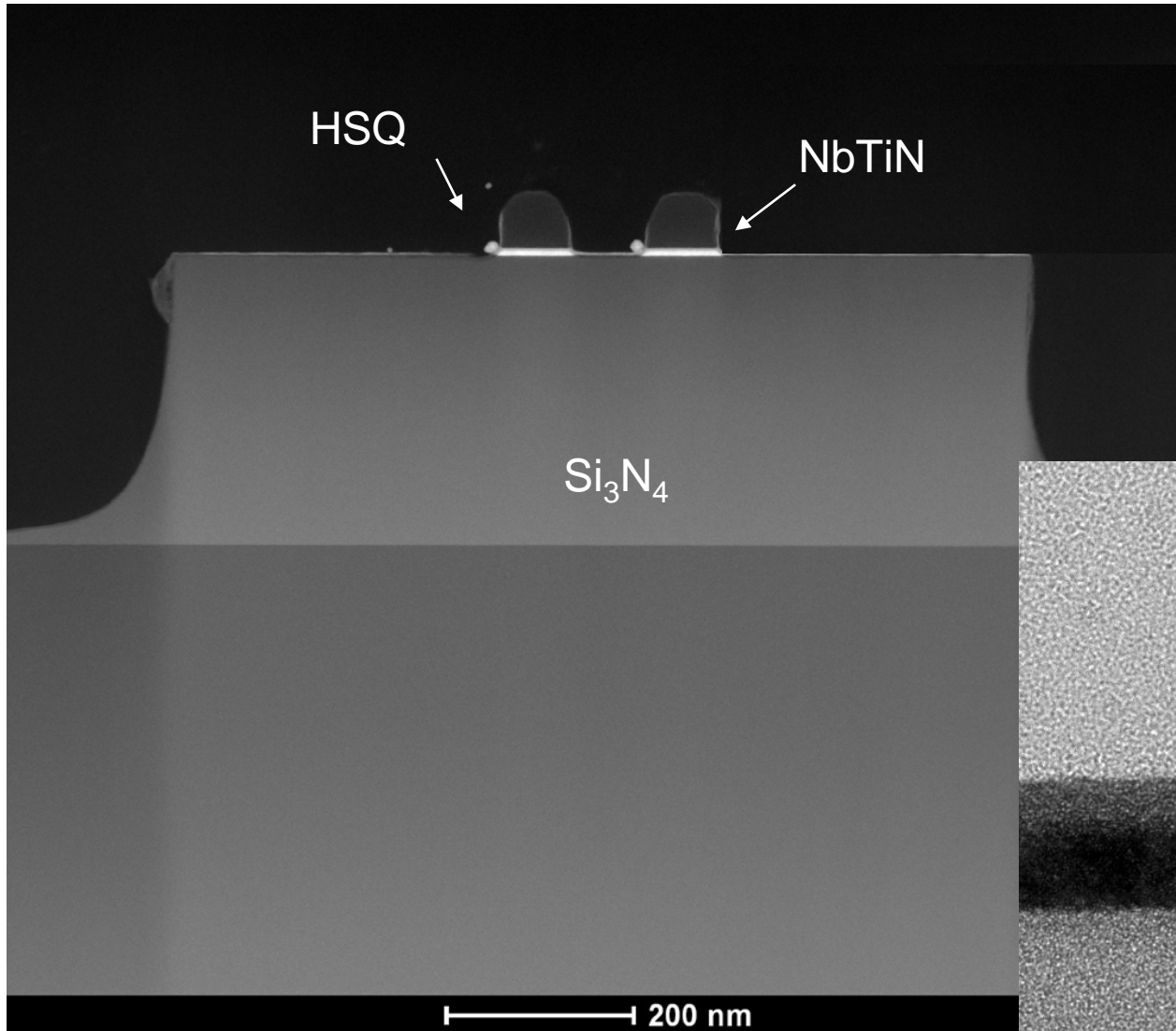
50ns-pulses  
10.5mW peak  
1550nm

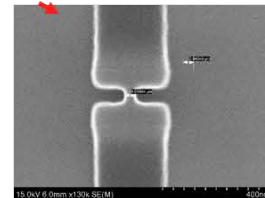
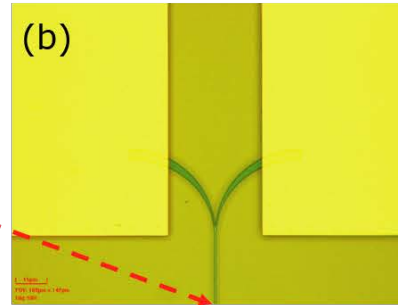
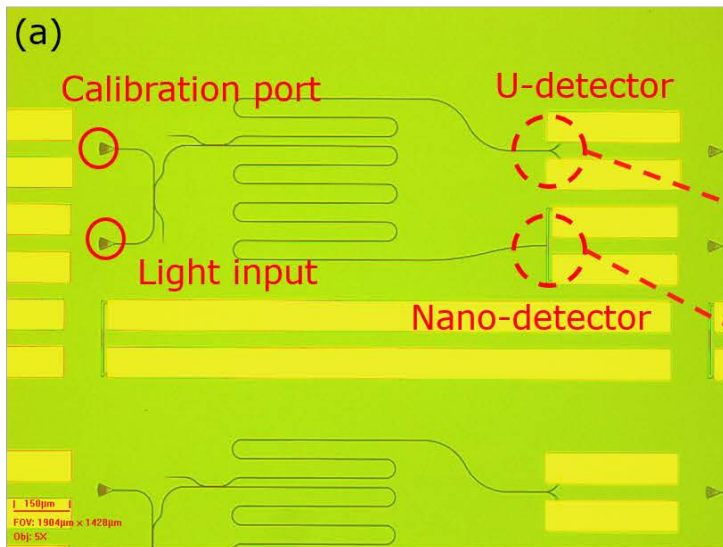
attenuation:  
0.196 dB/km

dynamic range:  
**37.4dB**

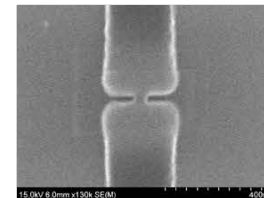
from last 30km of fiber  
→ DCR: 3Hz (→ NEP= $8 \times 10^{-18}$  W/Hz<sup>-1/2</sup>)

# TEM analysis of NbTiN detectors

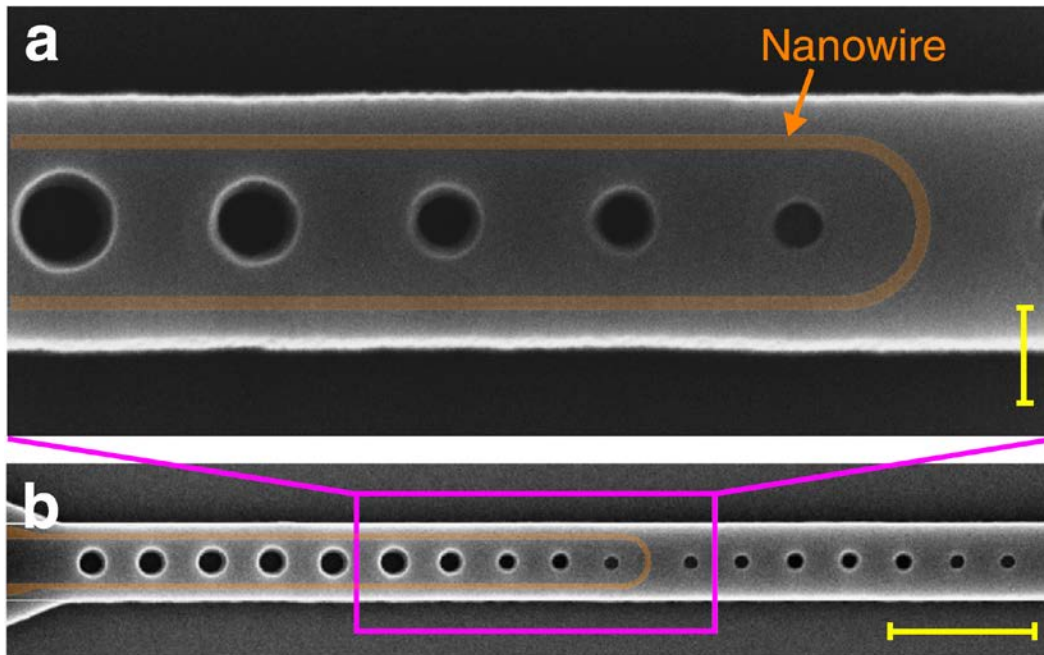
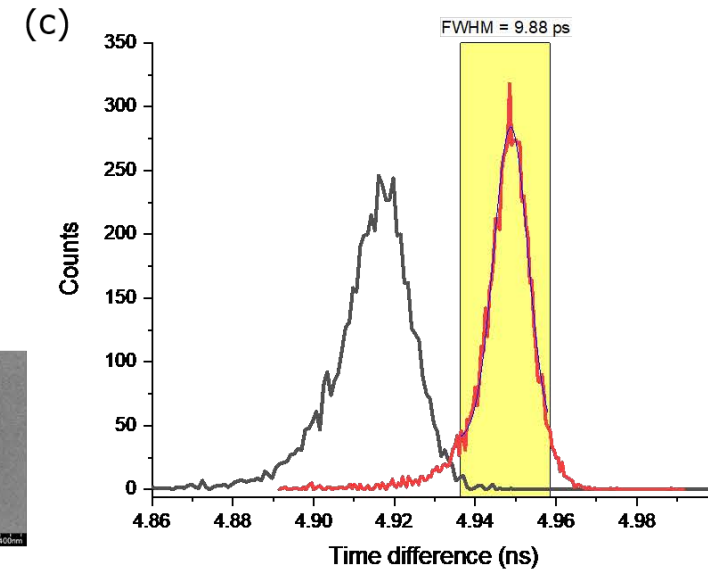




37nm



25nm



M.K. Akhlaghi, E. Schelew, J. F. Young, Nat. Comm. 6, 8233 (2015)

- Loaded  $Q = 275$ , photon lifetime = 1.4 ps (measured jitter: 63ps)
- Wire length 8µm



## Absorber design – Jitter consideration

**100fs**

= Light transits 30 $\mu$ m in free space

= Electrical signal propagation time in 1 $\mu$ m wire

→ To achieve better than 100fs jitter, we need to absorb all the light in 1 $\mu$ m travel distance

→ Cavity lifetime < 100fs, or  $Q < 20$

## Absorber design – efficiency consideration

**Quantum efficiency > 99% requires**

- Need 20dB absorption within 1 $\mu$ m length, or 20dB/ $\mu$ m
- No design can achieve such fast absorption → cavity is required
- Absorption in a cavity:  $\alpha LQ > 20dB$
- Considering  $L < 1\mu m$ ,  $Q < 20$  →  $\alpha > 1dB/\mu m$

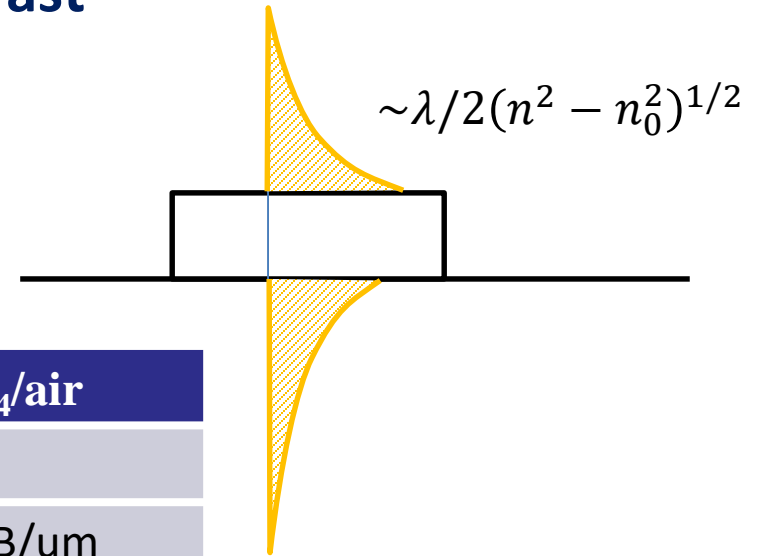


# Pathway to get 1dB/um absorption rate

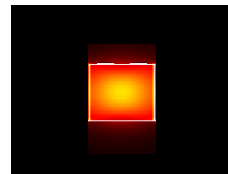
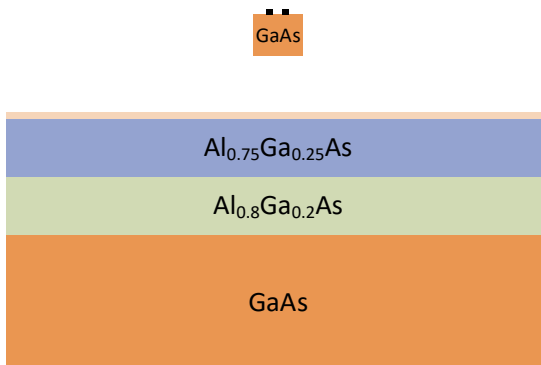


## Evanescent field should be large and decay fast

- High index contrast is key
- Air cladding is most desirable
- Aspect ratio, polarization are important



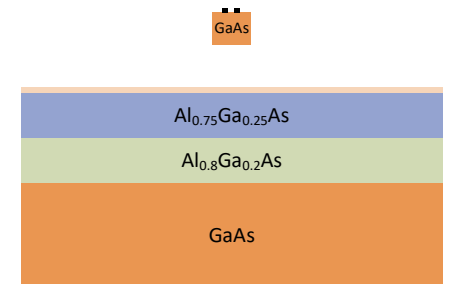
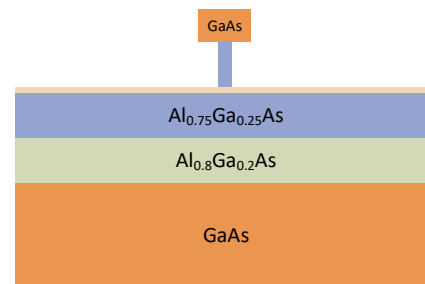
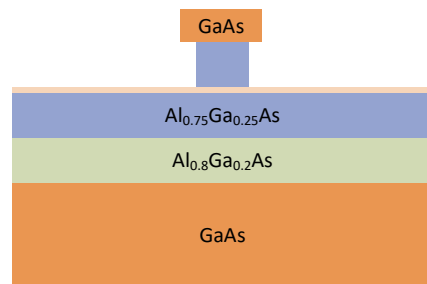
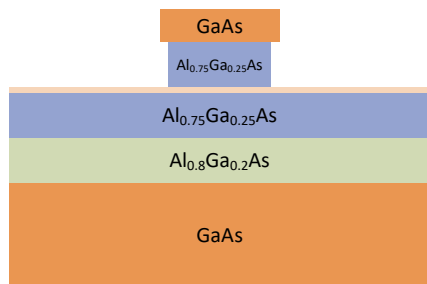
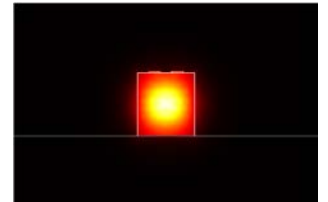
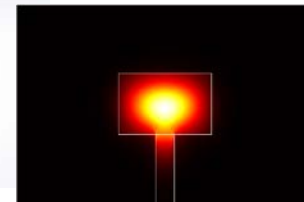
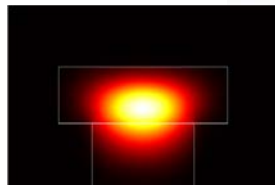
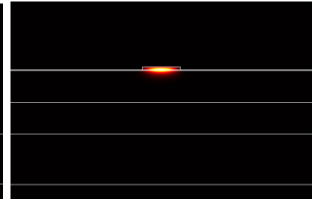
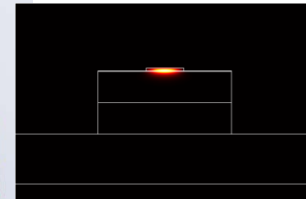
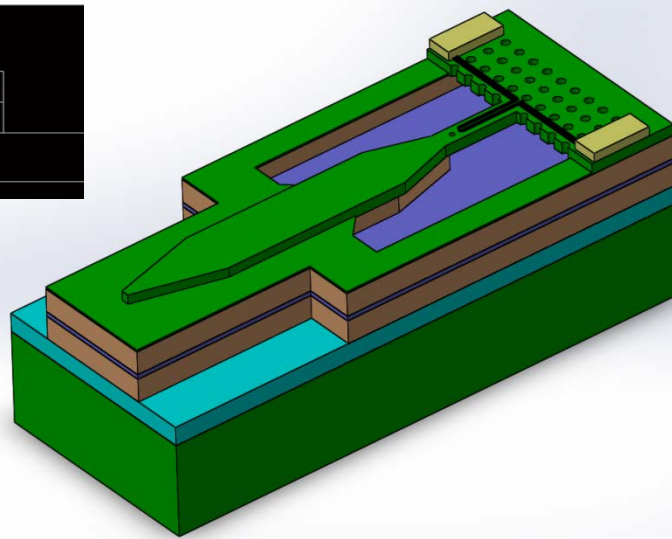
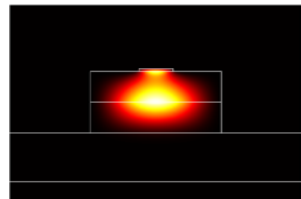
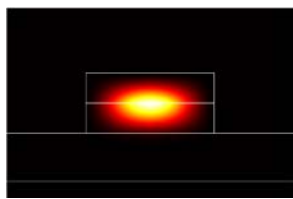
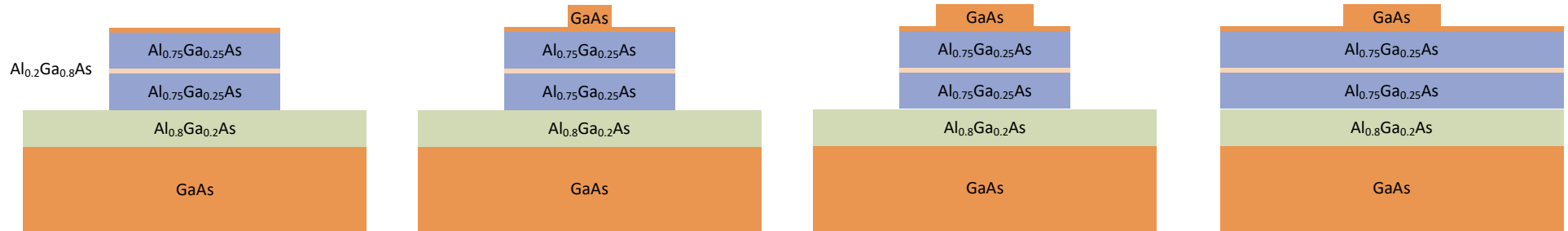
Waveguide	Si/air	GaAs/air	Si <sub>3</sub> N <sub>4</sub> /air
Index contrast	3.48/1	3.37/1	2.0/1
Absorption rate	1dB/um	1dB/um	0.6dB/um



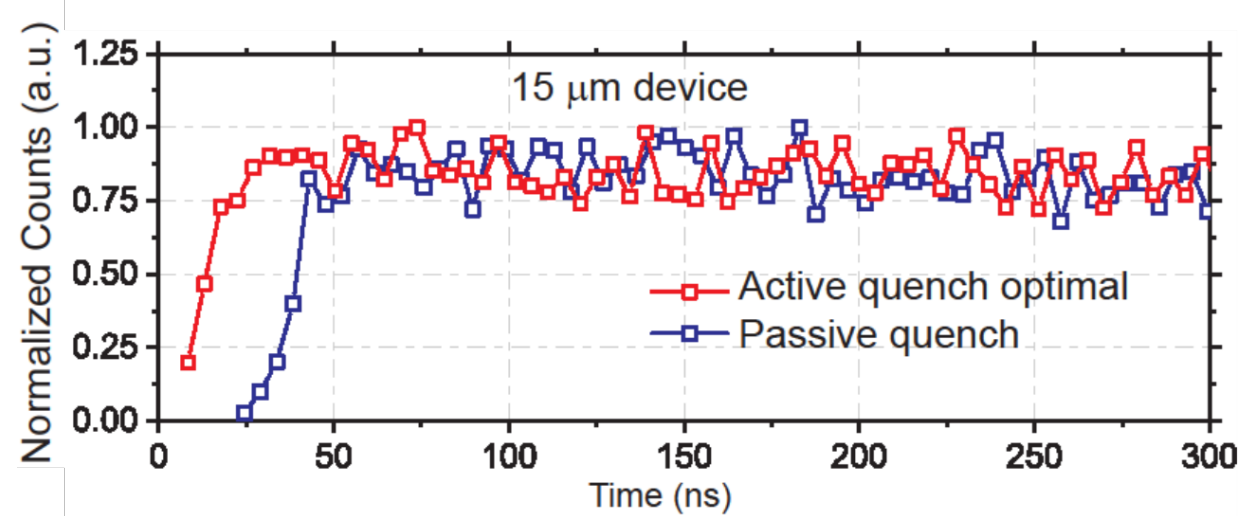
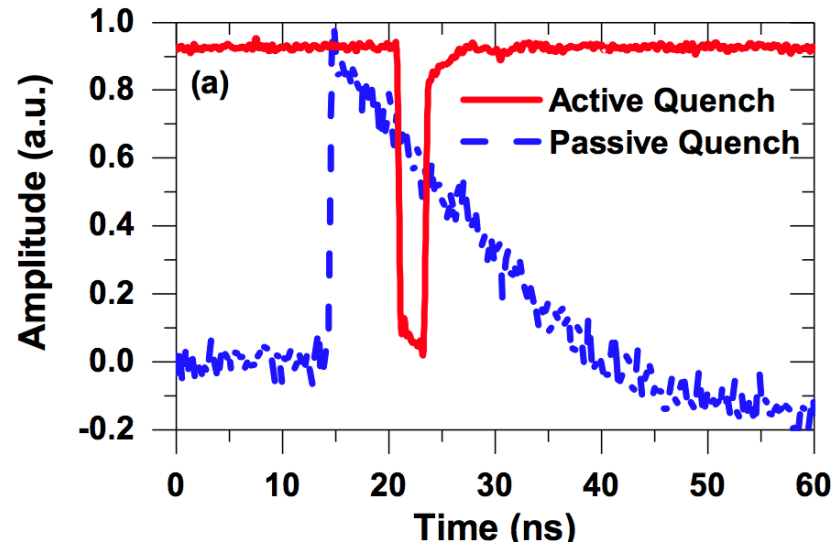
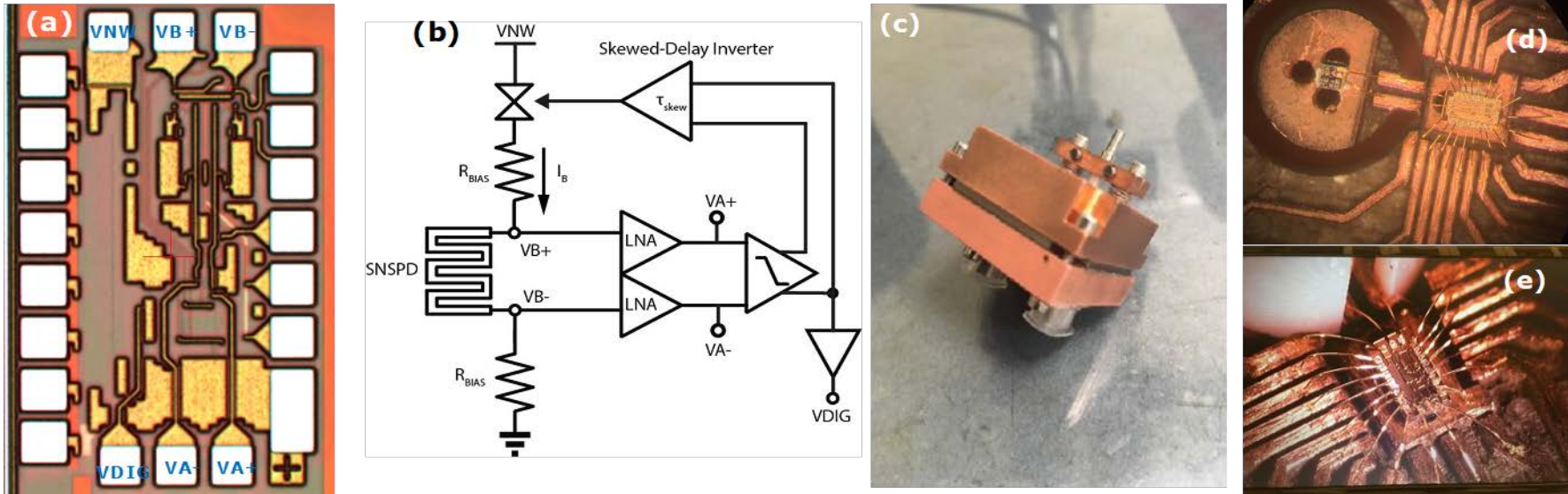
**60nm\*6nm NbTiN**  
on suspended GaAs  
waveguide with different  
thickness

Best results:  
**3.7dB/um** for TM  
2.3dB/um for TE

# High efficiency suspended GaAs waveguide



# Integrated detector readout



P. Ravindran, R. S. Cheng, H. X. Tang, J. C. Bardin, Optics Express, to be published.



## Powered by superconductor/photronics co-integration

### ❑ Waveguide integrated micro-SSPD

- Detector length  $\sim 10\mu\text{m}$ : high efficiency, speed, low jitter
- Integration in quantum photonic circuits
- v-ODTR

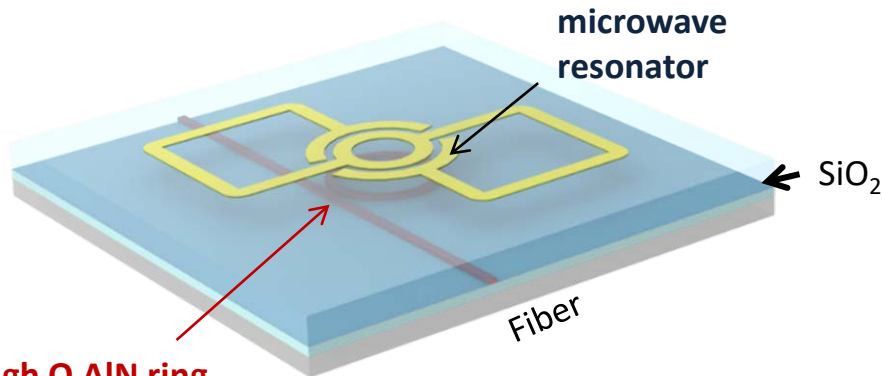
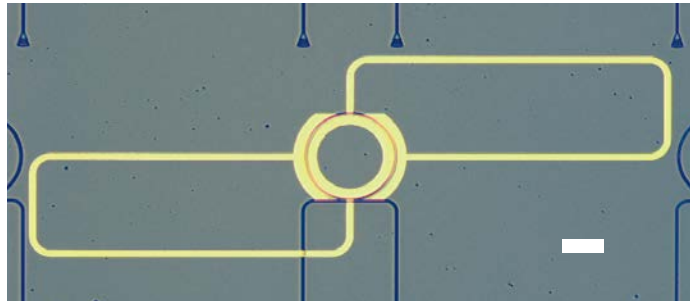
### ❑ Waveguide integrated nano-SSPD

- Detector length  $\sim 1\mu\text{m}$ , promising even higher speed

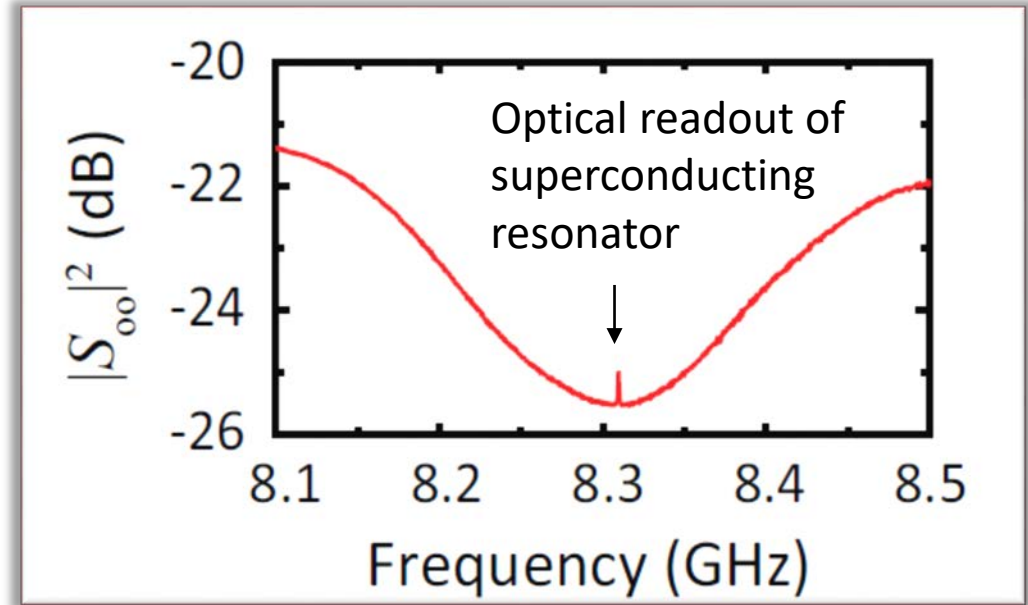
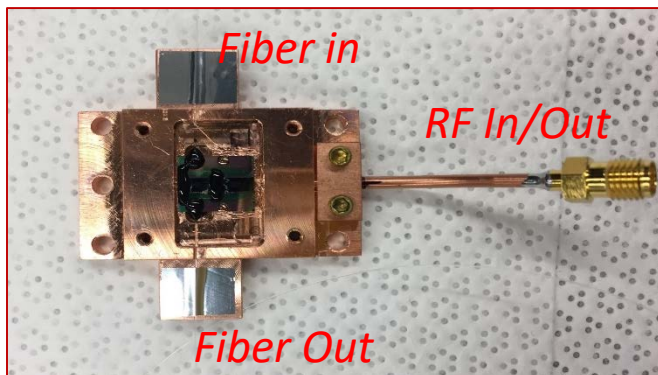
### ❑ Detector semiconductor chip integration

- Higher scalability, High counting rate

# Can we photodetect microwave photons?



High Q AlN ring resonator



L. R. Fan, C. Zou, R. Cheng, X. Guo, X. Han, Z. Gong, S. Wang, H. Tang, Science Advance, 4, 4994 (2018)

## Photodetect microwave photons

- Detection is already quantum limited
- No need for squid or JPA
- Current efficiency 2-26%
- Projected efficiency limited by coupling loss

# Thank you!



Risheng Cheng

Carsten Schuck (Assistant Prof., University of Munster), Xiaosong Ma (Professor Nanjing University), Wolfram Pernice (Professor, University of Munster)

Collaborators: Joseph Bardin (UMass), Zubin Jacobs (Purdue)

**Funded by:** DARPA (DETECT), NSF, Packard Foundation